11V Fast Startup With F0 Detect And Tracking LRA Haptic Driver

Features

- 1MHz I2C Bus
- 8-KByte Memory
- 12k/24k/48k input wave sampling rate
- F0 detect and tracking
- Advance autobrake engine integrated
- Playback mode:
  - Real time playback(Up to 4KByte FIFO)
  - Memory playback
  - 3 Trigger playback
  - One wire playback
  - Cont playback
- Resistance-Based LRA Diagnostics
- Drive signal monitor for LRA protect
- Drive Compensation Over Battery Discharge
- Fast Start Up Time ＜1ms
- Dedicated interrupt output pin
- Boost output voltage up to 11V
- VOUT=8.5V@Vbat=4.2V for 8Ω LRA
- Support automatically switch to standby mode
- Standby current：5μA@Vbat=3.6V
- Shutdown current：0.1μA
- Supply voltage range 3 to 5.5V
- Short-Circuit Protection, Over-Temperature Protection, Under-Voltage Protection
- FCQFN 2mm × 3mm × 0.55mm -20L Package
- AW86927NFCR included Immersion IP license for Notebook market

Applications

- Notebook

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General Description

AW86927N is a high voltage H-bridge, single chip LRA haptic driver, with F0 detecting and tracking based on BEMF, with a boost converter up to 11V drive voltage inside, supporting real time playback, memory playback, cont playback, one wire and hardware pin trigged playback. A typical startup time of 1ms makes the AW86927N an ideal haptic driver for fast responses.

AW86927N integrates a 8KByte SRAM for user-defined waveforms to achieve a variety of vibration experiences, supporting 3 sampling rate(12k/24k/48k) of waveforms loaded in SRAM, supporting output waveform sampling rate up-sampling to 48k.

AW86927N integrates an autobrake engine to suppress the aftershocks to zero for different drive waveforms(short or long) on different LRA motors.

AW86927N supports LRA fault diagnostic based on resistance measurement and protections of short-circuit, over-temperature and under-voltage.

AW86927N integrates a high-efficiency boost converter as the H-Bridge driver supply rail. The output voltage, maximum current limit and maximum boost current are configurable.

AW86927N features configurable automatically switch to standby mode after haptic waveform playback finished. This can less quiescent power consumption. The RSTN pin provides further power saving by fully shut down the whole device. Dedicated interrupt output pin can detect real time FIFO status and the error status of the chip.

AW86927N features general settings are communicated via an I2C-bus interface and its I2C address is configurable.

AW86927N is available in a FCQFN 2mm x 3mm x 0.55mm -20L package.

PIN CONFIGURATION AND TOP MARK

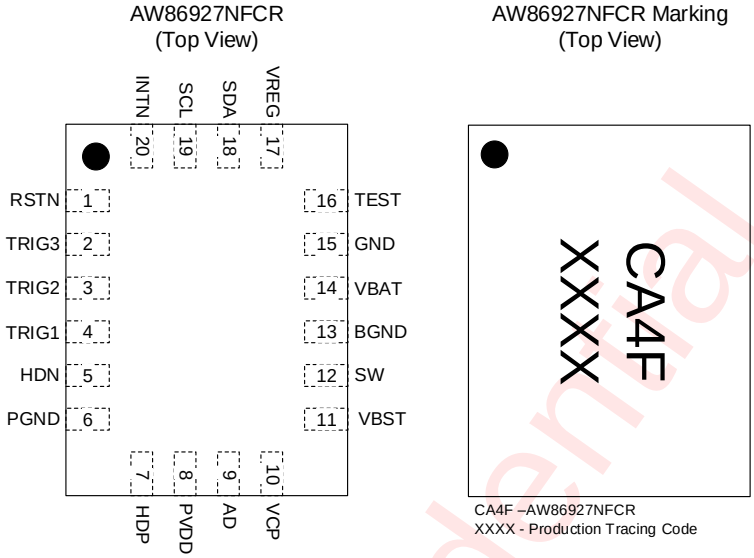


Figure 1 Pin Configuration and Top Mark

Pin Definition

No.	NAME	I/O	DESCRIPTION
1	RSTN	I	Active low hardware reset. High: standby/active mode, Low: power-down mode. Internal have 2MΩ pull-down resistor.
2	TRIG3	I	Hardware trigger 3. Internal have 2MΩ pull-down resistor.
3	TRIG2	I	Hardware trigger 2. Internal have 2MΩ pull-down resistor.
4	TRIG1	I	Hardware trigger 1. Internal have 2MΩ pull-down resistor.
5	HDN	O	Negative haptic driver differential output. Internal have 3KΩ pull-down resistor when standby/shutdown, high resistance when active.
6	PGND	Ground	H-bridge driver GND.
7	HDP	O	Positive haptic driver differential output. Internal have 3KΩ pull-down resistor when standby/shutdown, high resistance when active.
8	PVDD	Power	High voltage driver power rail output.
9	AD	I	I2C bus address selection. Internal have 2MΩ pull-down resistor.
10	VCP	O	Internal charge pump voltage.
11	VBST	Power	Boost output voltage output.
12	SW	O	Internal boost switch pin.
13	BGND	Ground	Boost GND.
14	VBAT	Power	Chip power supply.
15	GND	Ground	Supply ground.
16	TEST	IO	Test pin, default high resistance. Internal have 2MΩ pull-down resistor.
17	VREG	Power	Digital power supply output.
18	SDA	IO	I2C bus data input/output(open drain).
19	SCL	I	I2C bus clock input.
20	INTN	O	Interrupt open drain output, low active.

Functional Block Diagram

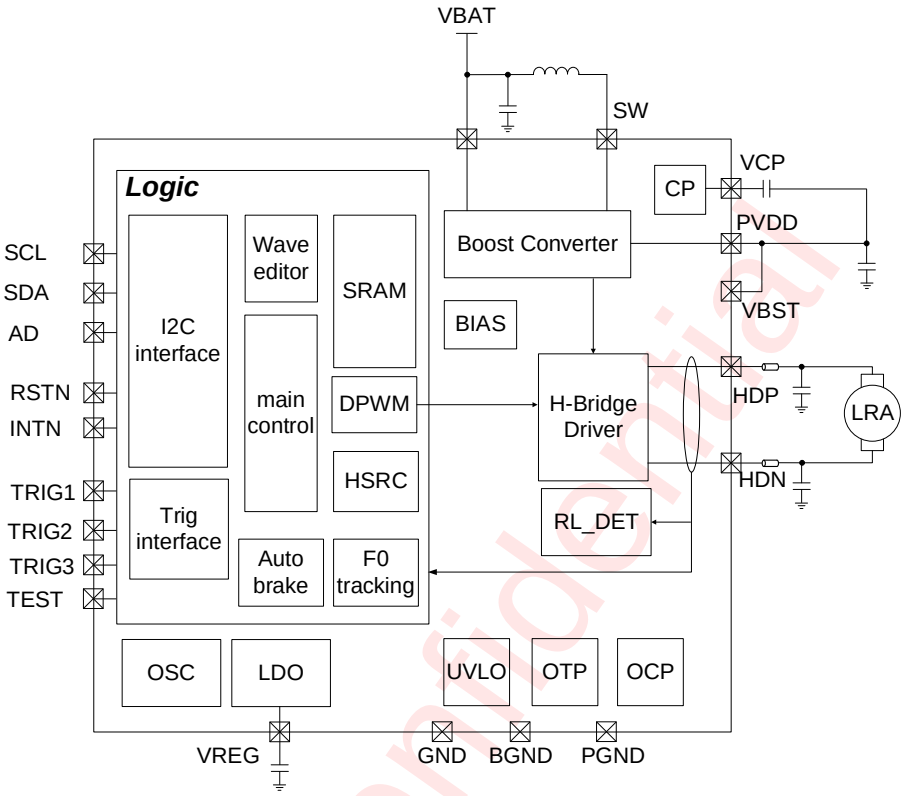


Figure 2 FUNCTIONAL BLOCK DIAGRAM

Typical Application Circuits

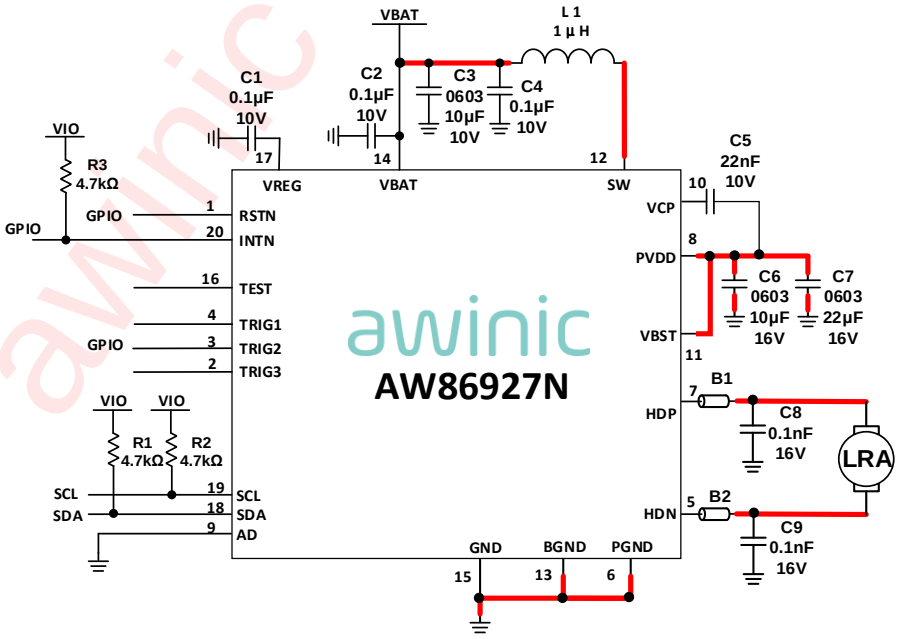


Figure 3 Typical Application Circuit of AW86927N

Notice for Typical Application Circuits:

1: Please place C1，C2，C3，C4，C5，C6，C7 as close to the chip as possible, and C6 and C7 close to PIN 11 and the capacitors should be placed in the same layer with the AW86927N chip.

2: For the sake of driving capability, the power lines (especially the one to Pin 12), output lines, and the connection lines of L1, and SW should be short and wide as possible. The power path marked in red as shown in the figures above. The peak current of VBAT to SW through L1 is about 3.75~4.0A, and the other red path traces according to 1.5A power line alignment rules.

Ordering Information

Part Number	Temperature	Package	Marking	Moisture Sensitivity Level	Environment Information	Delivery Form
AW86927NFCR	-40°C ~ 85°C	FCQFN 2mmX3mmX0.55mm-20L	CA4F	MSL1	ROHS+HF	6000 units/ Tape and Reel

Absolute Maximum Ratings(NOTE 1)

Parameter	Range
Battery Supply Voltage VBAT	-0.3V to 6.0V
Digital power supply VREG	-0.3V to 2.0V
Internal charge pump voltage VCP	-0.3V to 17V
Boost output voltage VBST PVDD	-0.3V to 13V
Internal boost switch pin SW	-0.3V to 15V
HDP, HDN	-0.3V to PVDD+0.3V
TRIG1/TRIG2/TRIG3/SDA/SCL/AD/INTN	-0.3V to 6V
TEST	-0.3V to VBAT+0.3V
Package Thermal Resistance θ_{JA}	60°C/W
Ambient Temperature Range	-40°C to 85°C
Maximum Junction Temperature T_{JMAX}	150°C
Storage Temperature Range T_{STG}	-65°C to 150°C
Lead Temperature(Soldering 10 Seconds)	260°C
ESD Rating (NOTE 2 3)	
HBM(Human Body Model)	±2KV
CDM(Charge Device Model)	±1.5KV
Latch-up	
Test Condition: JEDEC EIA/JESD78E	+IT: 200mA -IT: -200mA

NOTE 1: Conditions out of those ranges listed in "absolute maximum ratings" may cause permanent damages to the device. In spite of the limits above, functional operation conditions of the device should within the ranges listed in "recommended operating conditions". Exposure to absolute-maximum-rated conditions for prolonged periods may affect device reliability.

NOTE 2：The human body model is a 100pF capacitor discharged through a 1.5kΩ resistor into each pin. Test method: ANSI/ESDA/JEDEC JS-001-2017.

NOTE 3：Charge Device Model test method: ANSI/ESDA/JEDEC JS-002-2018.

Electrical Characteristics

Characteristics

Test condition: TA=25°C，VBAT=4.2V，PVDD=8V，RL=8Ω+100μH(unless otherwise noted)

Symbol	Description	Test Conditions	Min	Typ.	Max	Units
V_{VBAT}	Battery supply voltage	On pin VBAT	3		5.5	V
V_{VREG}	Voltage at VREG pin			1.5		V
V_{IL}	Logic input low level	RSTN/TRIG1/TRIG2/TRIG3/ AD/SCL/SDA			0.5	V
V_{IH}	Logic input high level	RSTN/TRIG1/TRIG2/TRIG3/ AD/SCL/SDA	1.3			V
V_{OL}	Logic output low level	INTN/SDA I_{OUT}=4mA			0.4	V
V_{OS}	Output offset voltage	I^2C signal input 0	-30	0	30	mV
I_{SD}	Shutdown current	VBAT=4.2V, RSTN =0V		0.1	1	μA
I_{STBY}	Standby current	VBAT=3.6V, AD= 0V TRIG1=TRIG2=TRIG3=0V RSTN=SCL=SDA=1.8V		5		μA
I_Q	Quiescent current	VBAT=3.6V@Bypass		3		mA
UVP	Under-voltage protection voltage			2.7		V
	Under-voltage protection hysteresis voltage			100		mV
T_{SD}	Over temperature protection threshold			160		°C
T_{SDR}	Over temperature protection recovery threshold			130		°C
T_{on1}	Time from shutdown to standby				8	ms
T_{on2}	Time from standby to active	From trigger to output signal			1	ms
Boost						
OVP	Over-voltage threshold			$1.1*V_{PVDD}$		
F_{BST}	Operating Frequency			2		MHz
I_{L_PEAK}	Inductor peak current limit			3.75		A
T_{ST}	Soft-start time	No load, COUT=20μF		0.3		ms
HDRIVER						
R_{DSON}	Drain-Source on-state resistance	Include H and L NMOS		300		mΩ

Symbol	Description	Test Conditions	Min	Typ.	Max	Units
R_{OCP}	Load impedance threshold for over current protection	VBAT=3.6V, PVDD=8V		2.5		Ω
F_{PWM}	PWM output frequency	VBAT=4.2V, PD_HWM=0		96		kHz
		VBAT=4.2V, PD_HWM=1		48		kHz
$F_{CALI\_ACC\_LRA}$	LRA Consistency Calibration accuracy		F0-2	F0	F0+2	Hz
V_{PEAK}	Output voltage	RL=16Ω+100μH VBAT=4.2V, PVDD set 11V		10.5		V
	Output voltage	RL=8Ω+100μH VBAT=4.2V, PVDD set 11V		8.5		V

I2C Interface Timing

Parameter			fast mode			fast mode plus			UNIT
No.	Symbol	Name	MIN	TYP	MAX	MIN	TYP	MAX	
1	f_{SCL}	SCL Clock frequency			400			1000	kHz
2	t_{LOW}	SCL Low level Duration	1.3			0.5			μs
3	t_{HIGH}	SCL High level Duration	0.6			0.26			μs
4	t_{RISE}	SCL, SDA rise time			0.3			0.12	μs
5	t_{FALL}	SCL, SDA fall time			0.3			0.12	μs
6	$t_{SU:STA}$	Setup time SCL to START state	0.6			0.26			μs
7	$t_{HD:STA}$	(Repeat-start) Start condition hold time	0.6			0.26			μs
8	$t_{SU:STO}$	Stop condition setup time	0.6			0.26			μs
9	t_{BUF}	the Bus idle time START state to STOP state	1.3			0.5			μs
10	$t_{SU:DAT}$	SDA setup time	0.1			0.1			μs
11	$t_{HD:DAT}$	SDA hold time	10			10			ns

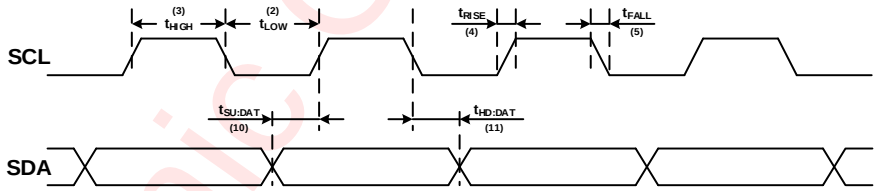


Figure 4 SCL and SDA timing relationships in the data transmission process

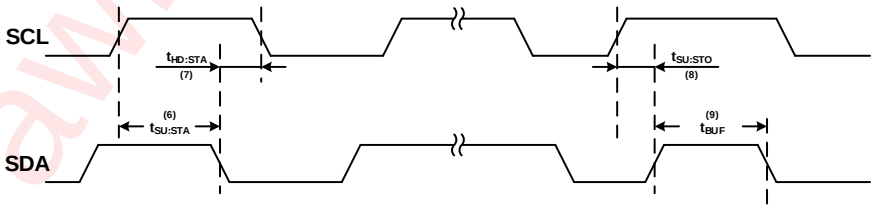


Figure 5 The timing relationship between START and STOP state

Measurement Setup

AW86927N features switching digital output, as shown in Figure 6. Need to connect a low pass filter to HDP/HDN output respectively to filter out switch modulation frequency, then measure the differential output of filter to obtain analog output signal.

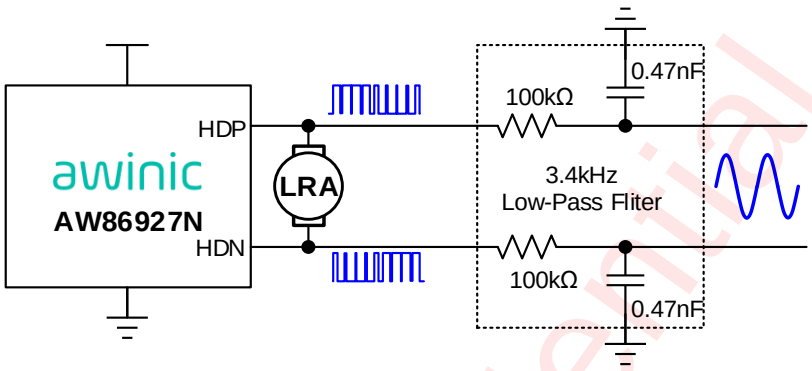


Figure 6 AW86927N test setup

Typical Characteristics

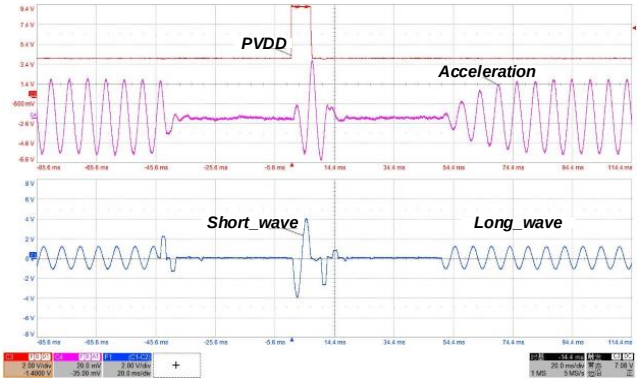


Figure 7 Long Vibration with Short Vibration insdie

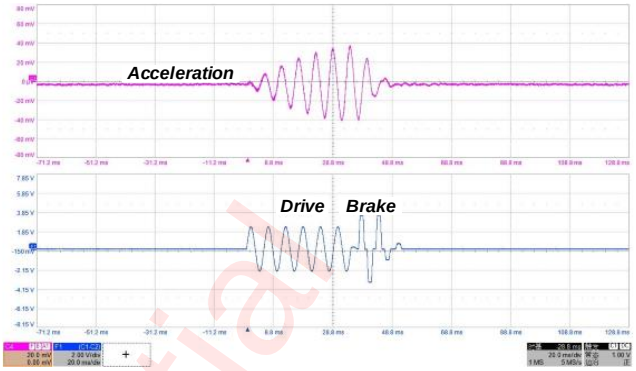


Figure 9 LRA with Automatic Braking

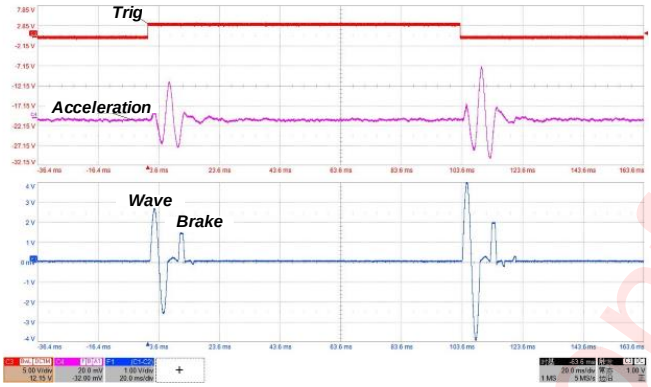


Figure 8 Trig Application

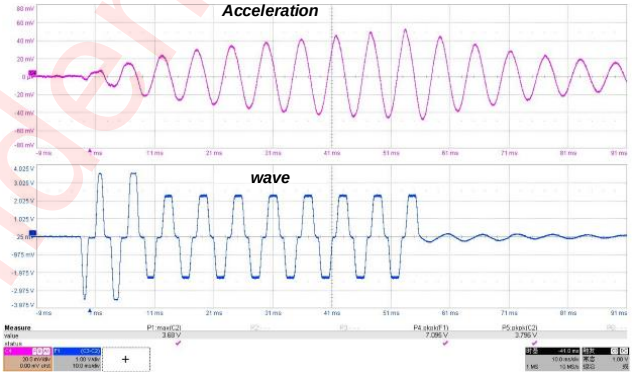


Figure 10 Automatic Resonance Tracking

Detailed Functional Description

Power On Reset

The device provides a power-on reset feature that is controlled by VREG OK. The reset signal will be generated to perform a power-on reset operation, which will reset all circuits and configuration registers. When the VBAT power on, the VREG voltage raises and produce the OK indication, the reset is over.

Operation Mode

The device supports 3 operation modes.

Table 1 Operating Mode

Mode	Condition	Description
Power-Down	VBAT = 0V or RSTN = 0V	Power supply is not ready or RSTN is tie to low. Whole chip shutdown including I²C interface.
Standby	VBAT > 2.7V and RSTN = HIGH and no wave is going	Power supply is ready and RSTN is tie to high. Most parts of the device are power down for low power consumption except I²C interface and LDO.
Active	Playing a waveform	Most parts of the device are working

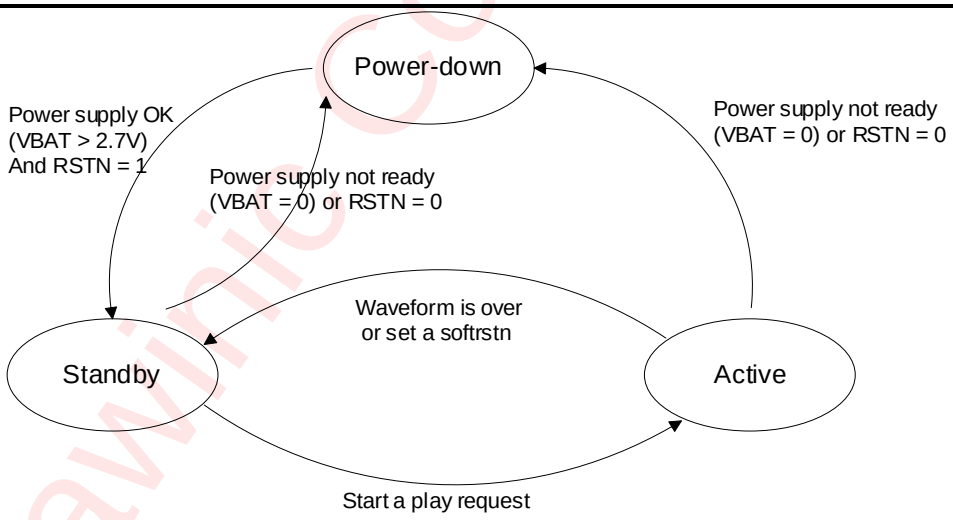


Figure 11 Device operating modes transition

POWER-DOWN MODE

The device switches to power-down mode when the supply voltage is not ready or RSTN pin is set to low.
In this mode, all circuits inside this device will be shut down. I²C interface isn't accessible in this mode, and all of the internal configurable registers and Memory are cleared.
The device will jump out of the power-down mode automatically when the supply voltages are OK and RSTN pin is set to high.

Standby Mode

The device switches standby mode when the power supply voltages are OK and RSTN pin set to high. In this mode I²C interface is accessible, other modules except LDO module are still powered down. Also in this mode, customer can initialize waveform library in SRAM. Device will be switched to this mode after haptic waveform playback finished.

Active Mode

The device is fully operational in this mode. Boost and H-bridge driver circuits will start to work. Users can send a playback request to make device in this mode.

Power On And Power Down Sequence

This device power on and power down sequence is illustrated in the following figure:

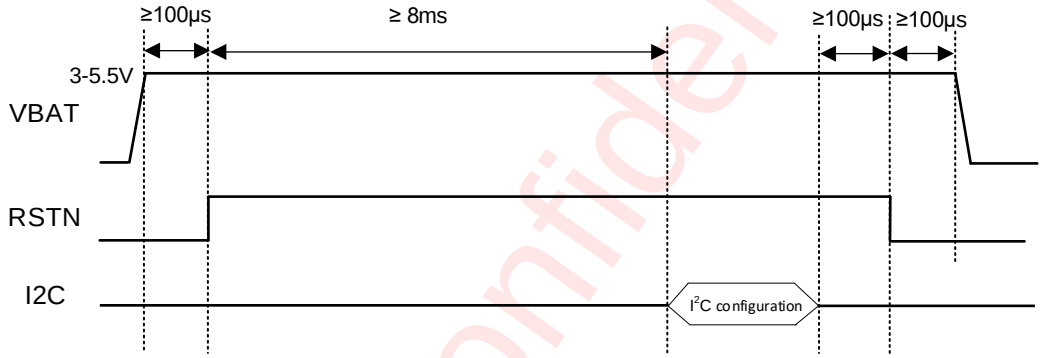


Figure 12 Power On and Power Down Sequence

Playback Sequence

Make sure the device is not in POWER-DOWN MODE before sending a playback request, then the playback sequence is illustrated in the following figure:

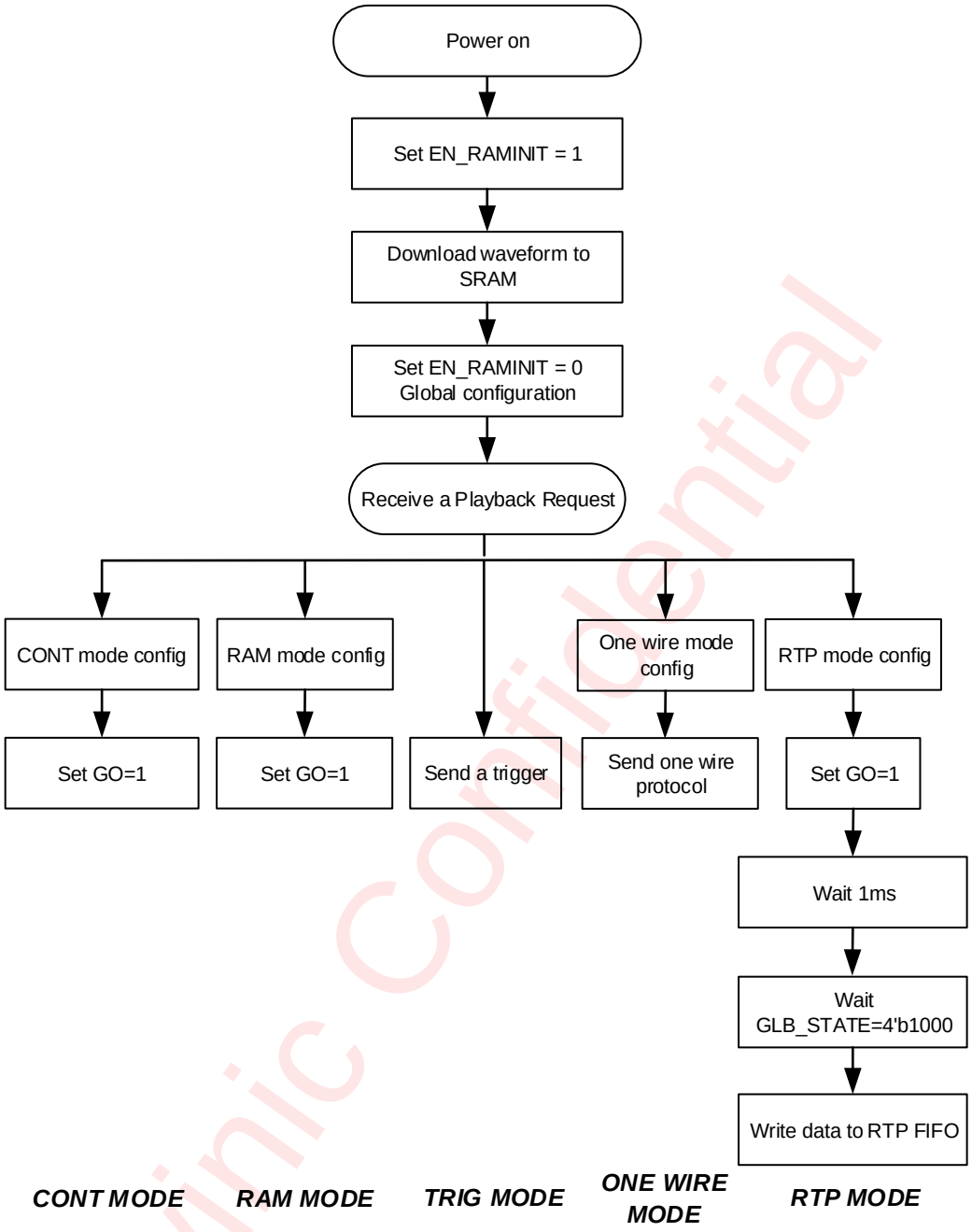


Figure 13 Power up and playback sequence

Software Reset

Writing 0xAA to register SOFTRST(0x00) via I²C interface will reset the device internal circuits except SRAM, including configuration registers.

Battery Voltage Detect

Software can send command to detect the battery voltage.

Detect steps:

- Set EN_RAMINIT to 1 in register 0x45;
- Set DET_SEQ0 to 0 in register 0x4e;

- Set DET_GO to 1 in register 0x4d;
- Wait 3ms;
- Set DET_GO to 0 in register 0x4d;
- Set EN_RAMINIT to 0 in register 0x45;
- Read AVG_DATA_H in register 0x4f and AVG_DATA_L in register 0x50. Code= AVG_DATA_H*256+ AVG_DATA_L.

The code is a 10bit unsigned number.

$$VBAT = \frac{6.08 \times code}{1024}(V)$$

Constant Vibration Strength

The device features power-supply feedback. If the supply voltage discharge over time, the vibration strength remains the same as long as enough supply voltage is available to sustain the required output voltage. It is especially useful for ring application. Power-supply feedback works in all playback mode.

Use steps:

- Set VBAT_REF in register 0x4d;
- Set VBAT_MODE to 1 in register 0x4c;
- Initiates a playback request.

LRA Consistency Calibration

Different motor batches, assembly conditions and other factors can result in f0 deviation of LRA. When the drive waveform does not match the LRA monomer, the vibration may be inconsistent and the braking effect becomes worse, especially for short vibration waveforms. So it's necessary to perform consistency calibration of LRA. Firstly the power-on f0 detection can be launched to get the f0 of LRA. Secondly the waveform frequency stored in SRAM and the f0 of LRA are used to calculate the code for calibration. The f0 accuracy after LRA consistency calibration is ±2Hz.

LRA Resistance Detect

Software can send command to detect the LRA's resistance.

Detect steps:

- Set EN_RAMINIT to 1 in register 0x45;
- Read D2S_GAIN register and save the result as d2s_gain_pre;
- Set DET_SEQ0 to 3 and set D2S_GAIN with an appropriate value in register 0x4e;
- Set DET_GO to 1 in register 0x4d;
- Wait 3ms;
- Set DET_GO to 0 in register 0x4d;
- Set EN_RAMINIT to 0 in register 0x45;
- Restore the value of D2S_GAIN register to d2s_gain_pre;
- Read AVG_DATA_H in register 0x4f and AVG_DATA_L in register 0x50. Code= AVG_DATA_H*256+ AVG_DATA_L.

Based on this code host can diagnosis used LRA's status. The code is a 10bit unsigned number.

$$RL = \frac{608 \times code}{1024 \times \text{D2S\_GAIN}}(\Omega)$$

The values of the D2S_GAIN that can be configured for different sizes of RL are listed below. The higher the RL, the smaller the configurable D2S_GAIN.

Table 2 D2S_GAIN Selection

RL(Ω)	D2S_GAIN
2~25	20
20~60	10

Flexible Haptic Data Playback

The device offers multiple ways to playback haptic effects data. The PLAY_MODE bits select RAM mode, RTP mode, CONT mode. Additional flexibility is provided by the three hardware TRIG pins, which can override PLAY_MODE bit to playback haptic effects data as configuration.

The device contains 8kB of integrated SRAM to store customer haptic waveforms' data. The whole SRAM is separated to RAM waveform library and RTP FIFO region by base address. And RAM waveform library is including waveform library version, waveform header and waveform data.

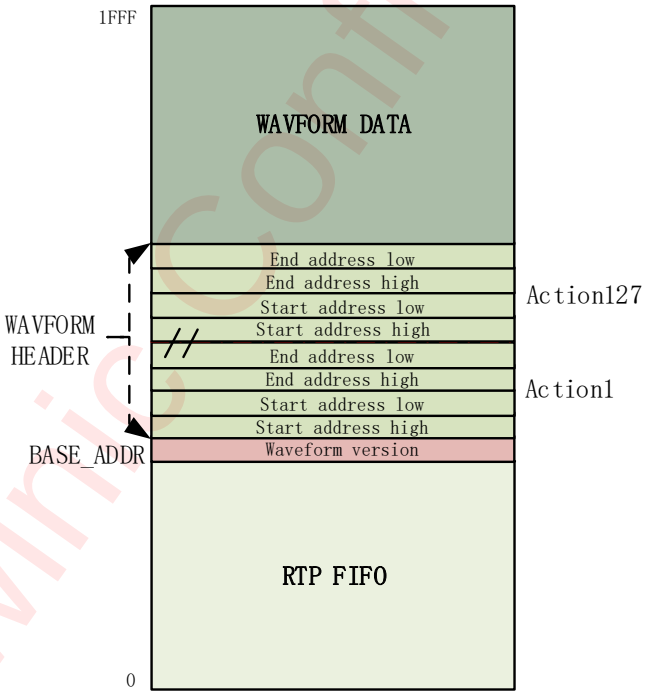


Figure 14 Data structure in SRAM

RAM mode and TRIG mode playback the waveforms in SRAM waveform library and RTP mode playback the waveform data written in RTP FIFO, CONT mode playback non-filtered or filtered square wave with rated drive voltage.

Sram Structure

A SRAM waveform library consists of a waveform version byte, a waveform header section, and the waveform data content. The waveform header defines the data boundaries for each waveform ID in the data field, and the waveform data contains a signed data format (2's complement) to specify the magnitude of the drive.

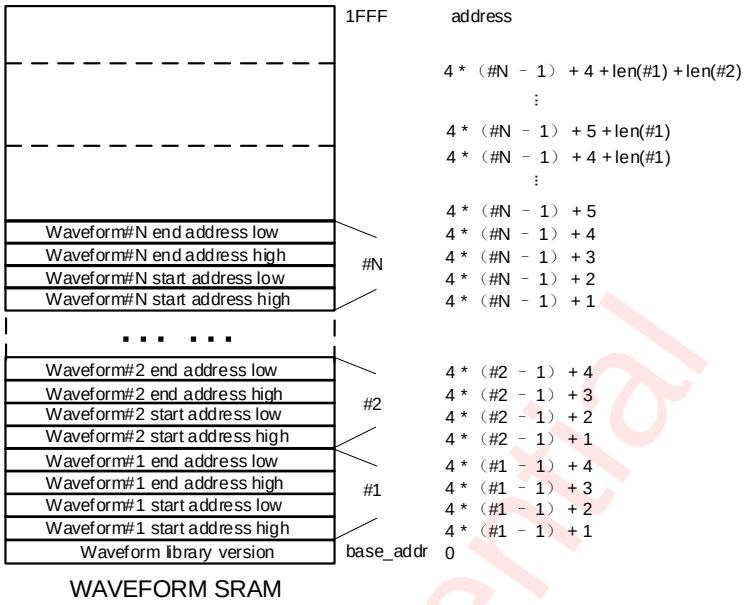


Figure 15 Waveform library data structure

Waveform version:

One byte located on SRAM base address, setting to different value to identify different version of RAM waveform library.

Waveform header:

The waveform header block consist of N-boundary definition blocks of 4 bytes each. N is the number of waveforms stored in the SRAM (N cannot exceed 127). Each of the boundary definition blocks contain the start address (2 bytes) and end address (2 bytes). So the total length of waveform header block are N*4 bytes.

The start address contains the location in the memory where the waveform data associated with this waveform begins.

The end address contains the location in the memory where the waveform data associated with this waveform ends.

The waveform ID is determined after base address is defined. Four bytes begins with the address next to base address are the first waveform ID's header, and next four bytes are the second waveform ID's header, and so on.

Waveform data:

The waveform data contains a signed data format (2's complement) to specify the magnitude of the drive. The begin address and end address is specified in waveform ID's header.

Waveform library initialization steps:

- Before waveform library initialization, make sure the chip is in STANDBY mode;
- Prepare waveform library data including: waveform library version, waveform header fields for waveform in library and waveform data of each waveform;
- Set register EN_RAMINIT=1 in register 0x45, open clock to enable SRAM initial;
- Delay 1ms;
- Set base address (register 0x2D, 0x2E);
- Set ram address (register 0x40, 0x41);

- Write waveform library data into register 0x42 continually until all the waveform library data written;
- Set register EN_RAMINIT=0, close clock to disable SRAM initial.

Ram Mode

To playback haptic data with RAM mode, the waveform ID must first be configured into the waveform playback queue and then the waveform can be played by writing GO bit register.

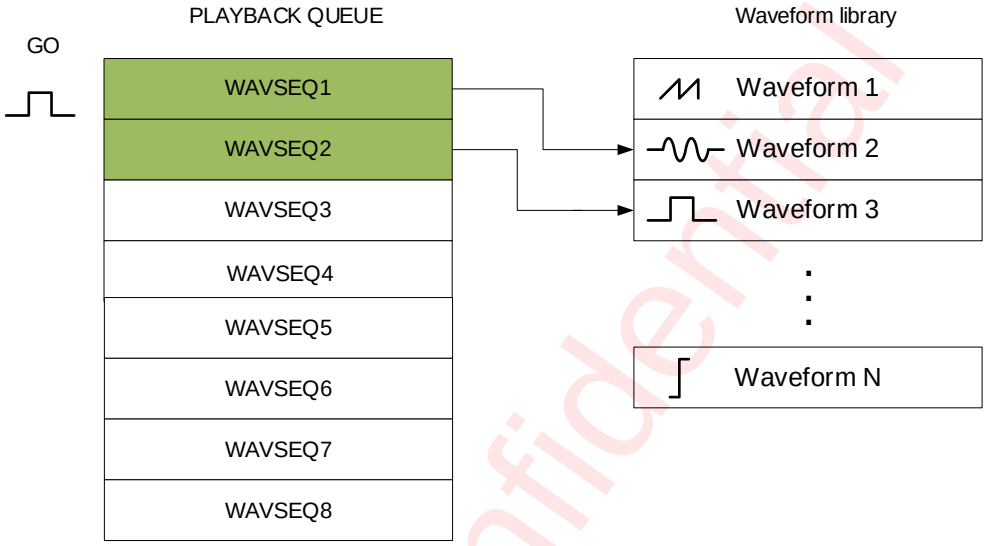


Figure 16 RAM mode playback

The waveform playback queue defines waveform IDs in waveform library for playback. Eight WAVSEQx registers queue up to eight library waveforms for sequential playback. A waveform ID is an integer value referring to the index of a waveform in the waveform library. Playback begins at WAVSEQ1 when the user triggers the waveform playback queue. When playback of that waveform ends, the waveform queue plays the next waveform ID held in WAVSEQ2 (if non-zero). The waveform queue continues in this way until the queue reaches an ID value of zero or until all eight IDs are played whichever comes first.

The waveform ID is a 7-bit number. The MSB of each ID register can be used to implement a delay between queue waveforms. When the SEQxWAIT is high, bits 6-0 indicate the length of the wait time. The wait time for that step then becomes WAVSEQ[6:0] × wait_time unit. Wait_time unit can be configuration of WAITSLOT register(in 0x16 register).

The device allows for looping of individual waveforms by using the SEQxLOOP registers. When used, the state machine will loop the particular waveform the number of times specified in the associated SEQxLOOP register before moving to the next waveform. The device allows for looping of the entire playback sequence by using the MAIN_LOOP register. The waveform-looping feature is useful for long, custom haptic playbacks, such as a haptic ringtone.

Playback steps:

- Waveform library must be initialized before playback;
- Set PLAY_MODE bits to 0 in register 0x08;
- Set playback queue registers (0x0A ~ 0x11) as desired;
- Set playback loop registers (0x12~ 0x16) as desired;
- Set GO bit to 1 in register 0x09 to trigger waveform playback;

- Device will be switched to STANDBY mode after haptic waveform playback finished.

Rtp Mode

The real-time playback mode is a simple, single 8-bit register interface that holds an amplitude value. When real-time playback is enabled, begin to enters a register value to RTP_DATA over the I²C will trigger the playback, the value is played until the data sending finished or removes the device from RTP mode. The maximum FIFO space is 4Kbyte. During writing data to the RTP_DATA register, the I2C speed cannot be too low, see the table below for details.

Table 3 Minimum I2C speed

WAVDAT_MODE(0x46)	Sample rate of waveform	I2C speed
2'b10/2'b11	12K	⩾250kHz
2'b00	24K	⩾400kHz
2'b01	48K	1MHz

After FF_AEM or FF_AFM register is set to 0, HOST can obtain the RTP FIFO almost empty or almost full status through interrupt signal(pin INTN) or read FF_AES or FF_AFS register. RTP FIFO almost empty and almost full threshold can be configured through FIFO_AE and FIFO_AF registers.

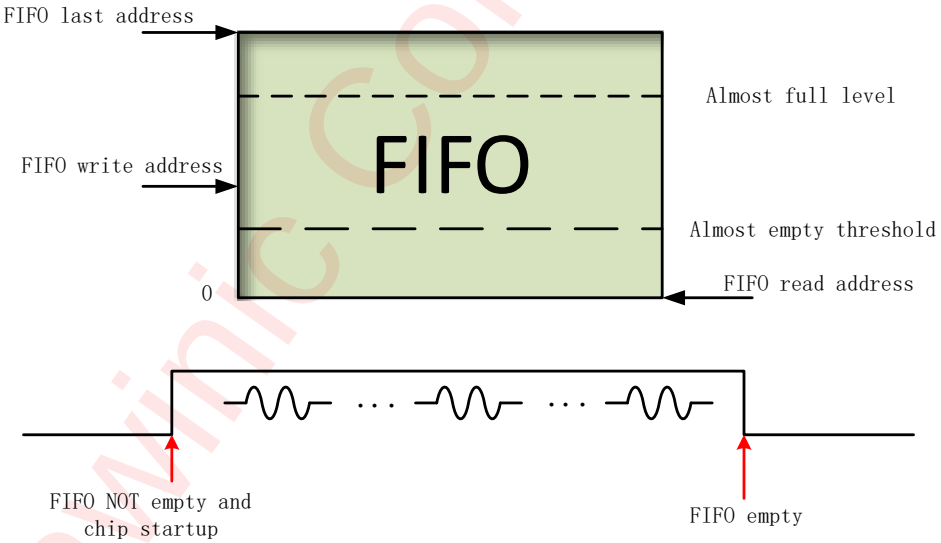


Figure 17 RTP mode playback

Playback steps:

- Prepare RTP data before playback;
- Set PLAY_MODE bit to 1 in register 0x08;
- Set GO bit to 1 in register 0x09 to trigger waveform playback;
- Delay 1ms.
- Check GLB_STATE=4'b1000，if HOST don't send data to FIFO, chip will wait for RTP data coming in this state forever;

- Write RTP data continually to register 0x32 to playback RTP waveform;
- HOST need monitor the almost full and almost empty status for RTP FIFO;
- Device will be switched to STANDBY mode after wave data in RTP FIFO is played empty.

Trig Mode

The device have three dedicated hardware pins for quickly trigger haptic data playback. Each pin can be configured posedge/negedge/both-edge/level trigger.

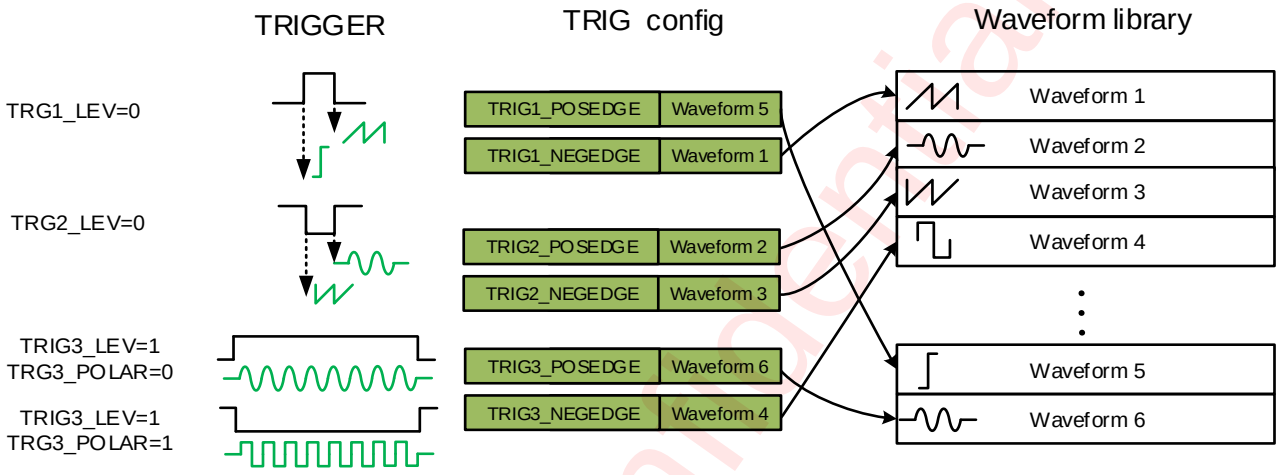


Figure 18 TRIG mode playback

Edge mode or level mode is accessible by configing register TRGx_LEV. When a edge mode is needed, user should set TRGx_LEV =0. In edge mode, register TRGxSEQ_P and TRGx_POS respestively represent the waveform and enable signal of positive edge, where register TRGxSEQ_N and TRGx_NEG respestively represent the waveform and enable signal of negative edge.

When a level mode is needed, user should set TRGx_LEV =1, and positive level and negative level can be supported by setting register TRGX_POLAR=0 and setting TRGX_POLAR=1.

Table 4 TRIG MODE CONFIG

I2C reg				Trigger	Waveform
TRGx_LVL	TRGx_POLAR	TRGx_POS	TRGx_NEG		
0	X	0	0	-	none
	X	1	0	↑	TRGxSEQ_P
	X	0	1	↓	TRGxSEQ_N
	X	1	1	↑ / ↓	TRGxSEQ_P/ TRGxSEQ_N
1	0	X	X	High level	TRGxSEQ_P
	1	X	X	Low level	TRGxSEQ_N

Playback steps:

- Waveform library must be initialized before playback;
- Set trigger playback registers (0x33 ~ 0x3A) as desired;
- Send trigger pulse ($\geq 1\mu s$) or trigger level ($\geq 1ms$) on TRIG pins to playback waveform;
- Device will be switched to STANDBY mode after haptic waveform playback finished.

One wire Mode

The function of one wire mode mainly transfer two information : sequence number and gain of waveform，TRIG1 is the interface pin.

Playback steps:

- Waveform library must be initialized before playback;
- Set TRG_ONEWIRE to 1 in register 0x3A to enable one wire mode;
- Determine sequence number and gain of waveform which you want to playback;
- Combine sequence number and gain data into a 15 bit transformation data（low 8 bit is gain, high 7 bit is sequence number），the data is sent from the lowest bit;
- Chip will automatically enter standby mode after playing. The interval time between two sending protocol data should be greater than “3ms+time length of waveform”.

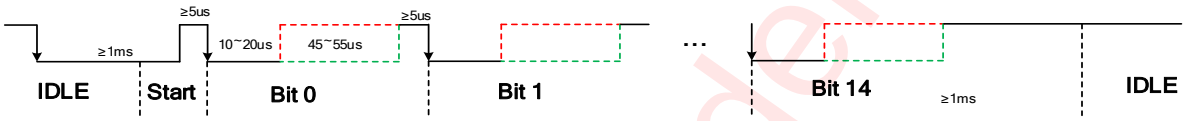


Figure 19 One wire mode playback

Cont Mode

The CONT mode mainly performs two functions: F0 detection and real-time resonance-frequency tracking. F0 detection can be launched by setting EN_F0_DET=1 and BRK_EN =1. When set TRACK_EN=1, real-time resonance-frequency tracking will be launched by tracking the BEMF of actuator constantly. It provides stronger and more consistent vibrations and lower power consumption. If the resonant frequency shifts for any reason, the function tracks the frequency from cycle to cycle. When TRACK_EN is set to 0, the width of waveform of cont mode is determined by DRV_WIDTH in register 0x1A.

When the EDGE_FRE register is set to 4’b1xxx, the CONT mode outputs a filtered square wave. The edge of filtered square wave is composed of SIN or COS wave whose frequency can be configured by EDGE_FRE register. When SIN_MODE register is set to 1, filtered square wave is composed of COS wave.

Playback steps:

- Set PLAY_MODE = 2 in register 0x08 to enable CONT mode;
- (optional)Set EN_F0_DET = 1 and BRK_EN =1 to enable F0 detection;
- Set cont mode by configuring registers(0x18~0x20 and 0x22);
- Set GO bit to 1 in register 0x09 to trigger waveform playback;
- Delay 1ms;
- If enable F0 detection, read until GLB_STATE=0. then get F0 information from registers(0x25~0x28);
- Device will be switched to STANDBY mode after haptic waveform playback finished.

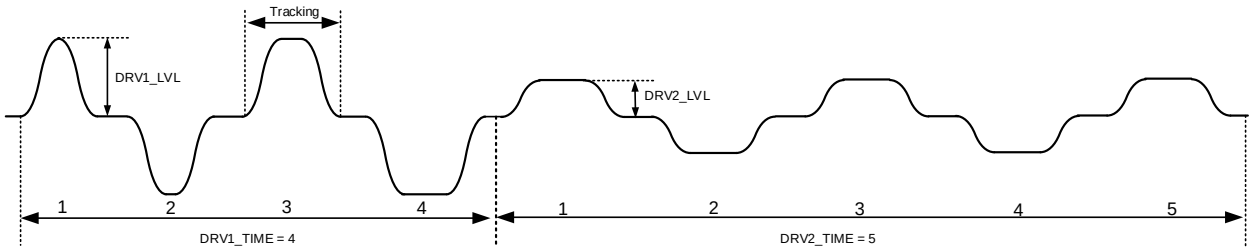


Figure 20 Cont mode playback

Auto Brake Engine

An auto-brake engine is integrated into this device. Users can adjust the brake strength by setting D2S_GAIN in register 0x4e. The greater D2S_GAIN, the greater brake strength and the worse loop stability. Auto-brake engine is disabled when setting BRK_EN=0 or BRK_TIME=0.

To enable Auto-brake engine, there are some points to note:

- TRGx_BRK in register 0x39, 0x3A should be set to 1 when in TRIG mode;
- Auto-brake engine will not work when BRK_EN=0 in register 0x08；
- Auto-brake engine will not work when EN_F0_DET in register 0x18 is set to 1;
- Auto-brake engine will not work when BRK_TIME in register 0x21 is set to 0;
- Device will be switched to STANDBY mode after haptic waveform playback finished.

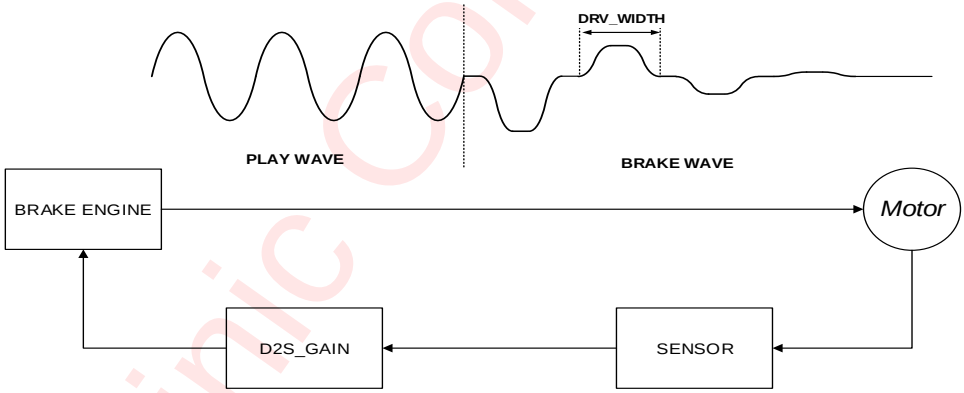


Figure 21 Brake loop

DC-DC Converter

The device integrated peak current mode synchronous PWM Boost as H-bridge power stage supply, significantly increase the output voltage dynamic range. Reduces the size of external components and saves PCB space by using about 2 MHz switching frequency. Boost output voltage can be set through the I^2C register 0x06;

The device synchronous Boost with soft-start function to prevent overshoot current at powering-on; integrated the output protection circuit and self-recovery function; integrated Anti-Ring circuit to reduce EMI in DCM mode; built-in substrate switching shutdown circuit, effectively preventing the input and output leakage current anti-irrigation.

Protection Mechanisms

Over Voltage Protection (OVP)

The boost circuit has integrated the over voltage protection control loop. When the output voltage PVDD is above the threshold, the boost circuits will stop working, until the voltage of PVDD going down and under the normal fixed working voltage.

Over Temperature Protection (OTP)

The device has automatic temperature protection mechanism which prevents heat damage to the chip. It is triggered when the junction temperature is larger than the preset temperature high threshold (default = 160°C). When it happens, the output stages will be disabled. When the junction temperature drops below the preset temperature low threshold (less than 130°C), the output stages will start to operate normally again

Over Current (Short) Protection (OCP)

The short circuit protection function is triggered when HDP/HDN is short too PVDD/GND or HDP is short to HDN, the output stages will be shut down to prevent damage to itself. When the fault condition is disappeared, the output stages of device will restart.

Vbat Under Voltage Lock Out Protection (UVLO)

The device has a battery monitor that monitors the VBAT level to ensure that is above threshold 2.7V, In the event of a VBAT drop, the device immediately power down the Boost and H-bridge driver and latches the UVLO flag.

Drive Data Error Protection (DDEP)

When haptic data sent to drive LRA is error such as: a DC data or almost DC data, it will cause the LRA heat to brake. The device configurable immediately power down the Boost and H-bridge driver and latched the DDEP flag.

I2C Interface

This device supports the I²C serial bus and data transmission protocol in fast mode at 400kHz and fast mode plus at 1000kHz. This device operates as a slave on the I²C bus. Connections to the bus are made via the open-drain I/O pin SDA and I pin SCL. The pull-up resistor can be selected in the range of 1k~10kΩ and the typical value is 4.7kΩ. This device can support different high level (1.8V~3.3V) of this I²C interface.

Device Address

The I²C device address (7-bit) can be set using the AD pin according to the following table:

Table 5 Address Selection

AD	I²C address (7-bit)
0	0x5A
1	0x5B

Data Validation

When SCL is high level, SDA level must be constant. SDA can be changed only when SCL is low level.

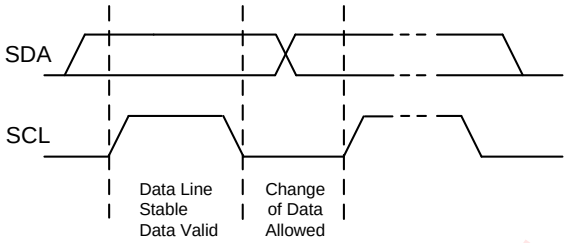


Figure 22 Data Validation Diagram

General I²C Operation

The I²C bus employs two signals, SDA (data) and SCL (clock), to communicate between integrated circuits in a system. The device is addressed by a unique 7-bit address; the same device can send and receive data. In addition, Communications equipment has distinguish master from slave device: In the communication process, only the master device can initiate a transfer and terminate data and generate a corresponding clock signal. The devices using the address access during transmission can be seen as a slave device.

SDA and SCL connect to the power supply through the current source or pull-up resistor. SDA and SCL default is a high level. There is no limit on the number of bytes that can be transmitted between start and stop conditions. When the last word transfers, the master generates a stop condition to release the bus.

START state: The SCL maintain a high level, SDA from high to low level

STOP state: The SCL maintain a high level, SDA pulled low to high level

Start and Stop states can be only generated by the master device. In addition, if the device does not produce STOP state after the data transmission is completed, instead re-generate a START state (Repeated START, Sr), and it is believed that this bus is still in the process of data transmission. Functionally, Sr state and START state is the same. As shown in Figure 23.

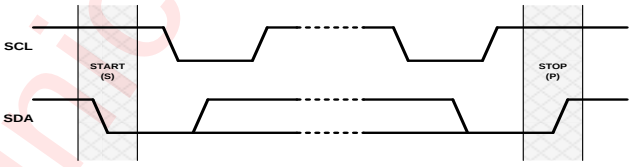


Figure 23 START and STOP state generation process

In the data transmission process, when the clock line SCL maintains a high level, the data line SDA must remain the same. Only when the SCL maintain a low level, the data line SDA can be changed, as shown in Figure 24. Each transmission of information on the SDA is 9 bits as a unit. The first eight bits are the data to be transmitted, and the first one is the most significant bit (Most Significant Bit, MSB), the ninth bit is an confirmation bit (Acknowledge, ACK or A), as shown in Figure 25. When the SDA transmits a low level in ninth clock pulse, it means the acknowledgment bit is 1, namely the current transmission of 8 bits data are confirmed, otherwise it means that the data transmission has not been confirmed. Any amount of data can be transferred between START and STOP state.

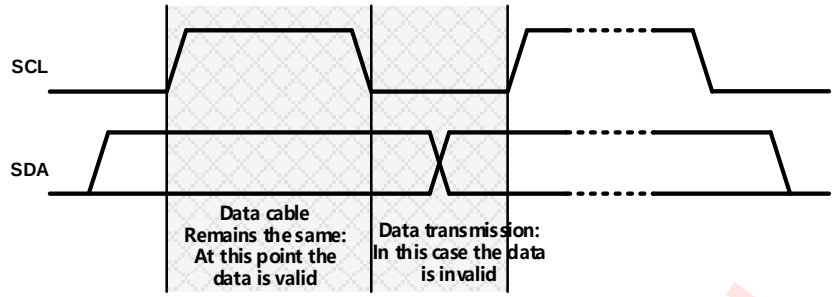


Figure 24 The data transfer rules on the I²C bus

The whole process of actual data transmission is shown in Figure 25. When generating a START condition, the master device sends an 8-bit data, including a 7-bit slave addresses (Slave Address), and followed by a "read / write" flag ($R/\overline{W}$). The flag is used to specify the direction of transmission of subsequent data. The master device will produce the STOP state to end the process after the data transmission is completed. However, if the master device intends to continue data transmission, you can directly send a Repeated START state, without the need to use the STOP state to end transmission.

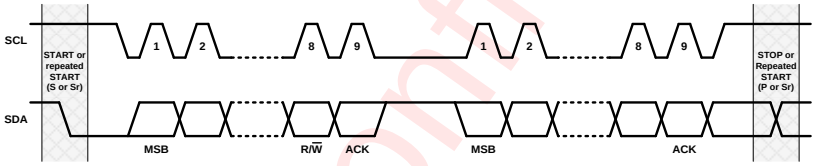


Figure 25 Data transmission on the I²C bus

Write Process

Writing process refers to the master device write data into the slave device. In this process, the transfer direction of the data is always unchanged from the master device to the slave device. All acknowledge bits are transferred by the slave device, in particular, the device as the slave device, the transmission process in accordance with the following steps, as shown in Figure 26:

Master device generates START state. The START state is produced by pulling the data line SDA to a low level when the clock SCL signal is a high level.

Master device transmits the 7-bits device address of the slave device, followed by the "read / write" flag (flag $R/\overline{W} = 0$);

The slave device asserts an acknowledgment bit (ACK) to confirm whether the device address is correct;

The master device transmits the 8-bit register address to which the first data byte will written；

The slave device asserts an acknowledgment (ACK) bit to confirm the register address is correct;

Master sends 8 bits of data to register which needs to be written;

The slave device asserts an acknowledgment bit (ACK) to confirm whether the data is sent successfully;

If the master device needs to continue transmitting data by sending another pair of data bytes, just need to repeat the sequence from step 6. In the latter case, the targeted register address will have been auto-incremented by the device.

The master device generates the STOP state to end the data transmission.

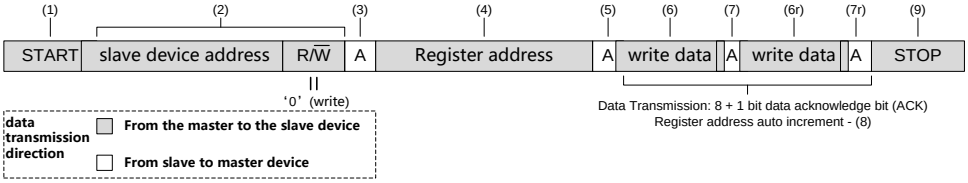


Figure 26 Writing process (data transmission direction remains the same)

Read Process

Reading process refers to the slave device reading data back to the master device. In this process, the direction of data transmission will change. Before and after the change, the master device sends START state and slave address twice, and sends the opposite "read/write" flag. In particular, AW86927N as the slave device, the transmission process carried out by following steps listed in Figure 27:
Master device asserts a start condition;

Master device transmits the 7 bits address of the device, and followed by a "read / write" flag ($R/\overline{W}$ = 0);
The slave device asserts an acknowledgment bit (ACK) to confirm whether the device address is correct;
The master device transmits the register address to make sure where the first data byte will read;
The slave device asserts an acknowledgment (ACK) bit to confirm whether the register address is correct or not;
The master device restarts the data transfer process by continuously generating STOP state and START state or a separate Repeated START;

Master sends 7-bits address of the slave device and followed by a read / write flag (flag $R/\overline{W}$ = 1) again;
The slave device asserts an acknowledgment (ACK) bit to confirm whether the register address is correct or not;
Master transmits 8 bits of data to register which needs to be read;
The slave device sends an acknowledgment bit (ACK) to confirm whether the data is sent successfully;
The device automatically increment register address once after sent each acknowledge bit (ACK),
The master device generates the STOP state to end the data transmission.

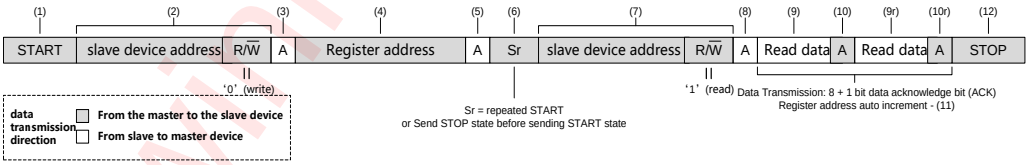


Figure 27 Reading process (data transmission direction remains the same)

Register Configuration

Register List

ADDR	NAME	R/W	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0	Default
0x00	RSTCFG	RW	SOFTRST								0x82
0x01	SYSST	RO			UVLS	FF_AES	FF_AFS	OCDS	OTS	DONES	0x10
0x02	SYSINT	RC			UVLI	FF_AEI	FF_AFI	OCDI	OTI	DONEI	0x10
0x03	SYSINTM	RW			UVLM	FF_AEM	FF_AFM	OCDM	OTM	DONEM	0xFF
0x06	PLAYCFG1	RW	BST_MODE	BST_VOUT_VREFSET							0x58
0x07	PLAYCFG2	RW	GAIN								0x80
0x08	PLAYCFG3	RW				AUTO_BST	STOP_MODE	BRK_EN	PLAY_MODE		0x14
0x09	PLAYCFG4	RW							STOP	GO	0x00
0x0A	WAVCFG1	RW	SEQ1WAIT	WAVSEQ1							0x01
0x0B	WAVCFG2	RW	SEQ2WAIT	WAVSEQ2							0x00
0x0C	WAVCFG3	RW	SEQ3WAIT	WAVSEQ3							0x00
0x0D	WAVCFG4	RW	SEQ4WAIT	WAVSEQ4							0x00
0x0E	WAVCFG5	RW	SEQ5WAIT	WAVSEQ5							0x00
0x0F	WAVCFG6	RW	SEQ6WAIT	WAVSEQ6							0x00
0x10	WAVCFG7	RW	SEQ7WAIT	WAVSEQ7							0x00
0x11	WAVCFG8	RW	SEQ8WAIT	WAVSEQ8							0x00
0x12	WAVCFG9	RW	SEQ1LOOP				SEQ2LOOP				0x00
0x13	WAVCFG10	RW	SEQ3LOOP				SEQ4LOOP				0x00
0x14	WAVCFG11	RW	SEQ5LOOP				SEQ6LOOP				0x00
0x15	WAVCFG12	RW	SEQ7LOOP				SEQ8LOOP				0x00
0x16	WAVCFG13	RW			WAITSLOT		MAINLOOP				0x00
0x18	CONTCFG1	RW		BRK_BST_MD	EN_F0_DET	SIN_MODE	EDGE_FRE				0x1E
0x19	CONTCFG2	RW	F_PRE								0x8D
0x1A	CONTCFG3	RW	DRV_WIDTH								0x6A
0x1C	CONTCFG5	RW	BST_BRK_GAIN				BRK_GAIN				0x58
0x1D	CONTCFG6	RW	TRACK_EN	DRV1_LVL							0xFF
0x1E	CONTCFG7	RW		DRV2_LVL							0x50
0x1F	CONTCFG8	RW	DRV1_TIME								0x04
0x20	CONTCFG9	RW	DRV2_TIME								0x06
0x21	CONTCFG10	RW	BRK_TIME								0x08
0x22	CONTCFG11	RW	TRACK_MARGIN								0x0C
0x25	CONTRD14	RO	F_LRA_F0_H								0x00
0x26	CONTRD15	RO	F_LRA_F0_L								0x00
0x27	CONTRD16	RO	CONT_F0_H								0x00
0x28	CONTRD17	RO	CONT_F0_L								0x00
0x2D	RTPCFG1	RW				BASE_ADDR_H					0x08
0x2E	RTPCFG2	RW	BASE_ADDR_L								0x00
0x2F	RTPCFG3	RW	FIFO_AEH				FIFO_AFH				0x26
0x30	RTPCFG4	RW	FIFO_AEL								0x00
0x31	RTPCFG5	RW	FIFO_AFL								0x00
0x32	RTPDATA	RW	RTP_DATA								0x00
0x33	TRGCFG1	RW	TRG1_POS	TRG1SEQ_P							0x01
0x34	TRGCFG2	RW	TRG2_POS	TRG2SEQ_P							0x01
0x35	TRGCFG3	RW	TRG3_POS	TRG3SEQ_P							0x01
0x36	TRGCFG4	RW	TRG1_NEG	TRG1SEQ_N							0x01
0x37	TRGCFG5	RW	TRG2_NEG	TRG2SEQ_N							0x01
0x38	TRGCFG6	RW	TRG3_NEG	TRG3SEQ_N							0x01
0x39	TRGCFG7	RW	TRG1_POLAR	TRG1_LEV	TRG1_BRK	TRG1_BST	TRG2_POLAR	TRG2_LEV	TRG2_BRK	TRG2_BST	0x33
0x3A	TRGCFG8	RW	TRG3_POLAR	TRG3_LEV	TRG3_BRK	TRG3_BST	TRG_ONEWIRE	TRG1_STOP	TRG2_STOP	TRG3_STOP	0x30
0x3C	GLBCFG2	RW	START_DLY								0x08
0x3E	GLBCFG4	RW	GO_PRIO		TRG3_PRIO		TRG2_PRIO		TRG1_PRIO		0x1B
0x3F	GLBRD5	RO					GLB_STATE				0x00

0x40	RAMADDRH	RW					RAMADDRH					0x00
0x41	RAMADDRL	RW	RAMADDRL									0x00
0x42	RAMDATA	RW	RAMDATA									0x00
0x45	SYSCTRL3	RW		WAKE	STANDBY				EN_RAMINIT	EN_FIR		0x12
0x46	SYSCTRL4	RW		WAVDAT_MODE								0x08
0x47	SYSCTRL5	RW	EN_BRO_ADR	BROADCAST_ADDR								0x00
0x48	PWMCFG1	RW	PRC_EN	PRCTIME								0x00
0x49	PWMCFG2	RW					PD_HWM					0x28
0x4A	PWMCFG3	RW	PR_EN	PRLVL								0xBF
0x4B	PWMCFG4	RW	PRTIME									0x32
0x4C	VBAT_CTRL	RW		VBAT_MODE								0x00
0x4D	DETCFG1	RW		VBAT_REF			ADC_FS		DET_GO			0x24
0x4E	DETCFG2	RW		DET_SEQ0				D2S_GAIN				0x04
0x4F	DET_RD1	RO					ADC_DATA_H		AVG_DATA_H			0x00
0x50	DET_RD2	RO	AVG_DATA_L									0x00
0x51	DET_RD3	RO	ADC_DATA_L									0x00
0x57	IDH	RO	CHIPID_H									0x92
0x58	IDL	RO	CHIPID_L									0x70

Register Detailed Description

Note: Reserved register should not be written

RSTCFG: (Address 00h)

Bit	Symbol	R/W	Description	Default
7:0	SOFTRST	RW	All configuration registers will be reset to default value after 0xaa is written	0x82

SYSST: (Address 01h)

Bit	Symbol	R/W	Description	Default
7:6	Reserved	RO	Not used	0
5	UVLS	RO	1: VBAT voltage is under UV voltage (2.7V)	0
4	FF_AES	RO	1: RTP FIFO is almost empty	1
3	FF_AFS	RO	1: RTP FIFO is almost full	0
2	OCDS	RO	1: Over Current status	0
1	OTS	RO	1: Over Temperature status	0
0	DONES	RO	1: The indication of playback finished	0

SYSINT: (Address 02h)

Bit	Symbol	R/W	Description	Default
7:6	Reserved	RC	Not used	0
5	UVLI	RC	When UVLI=1, it means UVLS has been 1 at least once since the last read	0
4	FF_AEI	RC	When FF_AEI=1, it means FF_AES has been 1 at least once since the last read	1
3	FF_AFI	RC	When FF_AFI=1, it means FF_AFS has been 1 at least once since the last read	0
2	OCDI	RC	When OCDI=1, it means OCDS has been 1 at least once since the last read	0
1	OTI	RC	When OTI=1, it means OTS has been 1 at least once since the last read	0
0	DONEI	RC	When DONEI=1, it means DONES has been 1 at least once since the last read	0

SYSINTM: (Address 03h)

Bit	Symbol	R/W	Description	Default
7:6	Reserved	RW	Not used	3
5	UVLM	RW	Interrupt mask for UVLI: 0: INTN pin will be pulled down when UVLI=1 1: INTN pin will not be pulled down when UVLI=1	1

4	FF_AEM	RW	Interrupt mask for FF_AEI: 0: INTN pin will be pulled down when FF_AEI=1 1: INTN pin will not be pulled down when FF_AEI=1	1
3	FF_AFM	RW	Interrupt mask for FF_AFI: 0: INTN pin will be pulled down when FF_AFI=1 1: INTN pin will not be pulled down when FF_AFI=1	1
2	OCDM	RW	Interrupt mask for OCDI: 0: INTN pin will be pulled down when OCDI=1 1: INTN pin will not be pulled down when OCDI=1	1
1	OTM	RW	Interrupt mask for OTI: 0: INTN pin will be pulled down when OTI=1 1: INTN pin will not be pulled down when OTI=1	1
0	DONEM	RW	Interrupt mask for DONEI: 0: INTN pin will be pulled down when DONEI=1 1: INTN pin will not be pulled down when DONEI=1	1

PLAYCFG1: (Address 06h)

Bit	Symbol	R/W	Description	Default
7	BST_MODE	RW	BOOST mode 0: Bypass mode 1: Boost mode	0
6:0	BST_VOUT_VREFSET	RW	PVDD voltage setup: ΔV=62.5mV, default=9V VBAT should be smaller than 0.8*PVDD and PVDD > 6V b0000000~b0100111: code can not be configured b0101000: 6V (3.5V+ΔV*40) b0101001: 3.5V+ΔV*41 b0101010: 3.5V+ΔV*42 ..... b1111111: 11.4375V (3.5V+ΔV*127)	0x58

PLAYCFG2: (Address 07h)

Bit	Symbol	R/W	Description	Default
7:0	GAIN	RW	Gain setting for waveform data of RAM mode, GAIN=code/128	0x80

PLAYCFG3: (Address 08h)

Bit	Symbol	R/W	Description	Default
7:5	Reserved	RW	Not used	0
4	AUTO_BST	RW	1: disable Boost when data is 0 in RTP and RAM mode	1
3	STOP_MODE	RW	0: stop when current wave is over 1: stop right now	0
2	BRK_EN	RW	When set 1, enable auto brake after RTP/RAM/CONT playback mode is stopped	1
1:0	PLAY_MODE	RW	Waveform play mode for GO trig b00: RAM mode b01: RTP mode b10: CONT mode b11: no play	0

PLAYCFG4: (Address 09h)

Bit	Symbol	R/W	Description	Default
7:2	Reserved	RW	Not used	0
1	STOP	RW	When set 1, stop the current playback mode	0
0	GO	RW	RAM/RTP/CONT mode playback trig bit when set to 1, chip will playback one of the play mode.	0

WAVCFG1: (Address 0Ah)

Bit	Symbol	R/W	Description	Default
7	SEQ1WAIT	RW	When set to 1 , WAVSEQ1 means wait time, else means wave sequence number	0
6:0	WAVSEQ1	RW	Wait time (code*WAITSLOT) or wave sequence number	1

WAVCFG2: (Address 0Bh)

Bit	Symbol	R/W	Description	Default
7	SEQ2WAIT	RW	When set to 1 , WAVSEQ2 means wait time, else means wave sequence number	0
6:0	WAVSEQ2	RW	Wait time (code*WAITSLOT) or wave sequence number	0

WAVCFG3: (Address 0Ch)

Bit	Symbol	R/W	Description	Default
7	SEQ3WAIT	RW	When set to 1 , WAVSEQ3 means wait time, else means wave sequence number	0
6:0	WAVSEQ3	RW	Wait time (code*WAITSLOT) or wave sequence number	0

WAVCFG4: (Address 0Dh)

Bit	Symbol	R/W	Description	Default
7	SEQ4WAIT	RW	When set to 1 , WAVSEQ4 means wait time, else means wave sequence number	0
6:0	WAVSEQ4	RW	Wait time (code*WAITSLOT) or wave sequence number	0

WAVCFG5: (Address 0Eh)

Bit	Symbol	R/W	Description	Default
7	SEQ5WAIT	RW	when set to 1 , WAVSEQ5 means wait time, else means wave sequence number	0
6:0	WAVSEQ5	RW	Wait time (code*WAITSLOT) or wave sequence number	0

WAVCFG6: (Address 0Fh)

Bit	Symbol	R/W	Description	Default
7	SEQ6WAIT	RW	When set to 1 , WAVSEQ6 means wait time, else means wave sequence number	0
6:0	WAVSEQ6	RW	Wait time (code*WAITSLOT) or wave sequence number	0

WAVCFG7: (Address 10h)

Bit	Symbol	R/W	Description	Default
7	SEQ7WAIT	RW	when set to 1 , WAVSEQ7 means wait time, else means wave sequence number	0
6:0	WAVSEQ7	RW	Wait time (code*WAITSLOT) or wave sequence number	0

WAVCFG8: (Address 11h)

Bit	Symbol	R/W	Description	Default
7	SEQ8WAIT	RW	When set to 1 , WAVSEQ8 means wait time, else means wave sequence number	0
6:0	WAVSEQ8	RW	Wait time (code*WAITSLOT) or wave sequence number	0

WAVCFG9: (Address 12h)

Bit	Symbol	R/W	Description	Default
7:4	SEQ1LOOP	RW	Control the loop number of the first sequence b0000~b1110: play (code+1) time b1111: playback infinitely until STOP set to 1 or SEQ1LOOP ≠0xF	0
3:0	SEQ2LOOP	RW	Control the loop number of the second sequence b0000~b1110: play (code+1) time b1111: playback infinitely until STOP set to 1 or SEQ2LOOP ≠0xF	0

WAVCFG10: (Address 13h)				
Bit	Symbol	R/W	Description	Default
7:4	SEQ3LOOP	RW	Control the loop number of the third sequence b0000~b1110: play (code+1) time b1111: playback infinitely until STOP set to 1 or SEQ3LOOP ≠0xF	0
3:0	SEQ4LOOP	RW	Control the loop number of the fourth sequence b0000~b1110: play (code+1) time b1111: playback infinitely until STOP set to 1 or SEQ4LOOP ≠0xF	0

WAVCFG11: (Address 14h)				
Bit	Symbol	R/W	Description	Default
7:4	SEQ5LOOP	RW	Control the loop number of the fifth sequence b0000~b1110: play (code+1) time b1111: playback infinitely until STOP set to 1 or SEQ5LOOP ≠0xF	0
3:0	SEQ6LOOP	RW	Control the loop number of the sixth sequence b0000~b1110: play (code+1) time b1111: playback infinitely until STOP set to 1 or SEQ6LOOP ≠0xF	0

WAVCFG12: (Address 15h)				
Bit	Symbol	R/W	Description	Default
7:4	SEQ7LOOP	RW	Control the loop number of the seventh sequence b0000~b1110: play (code+1) time b1111: playback infinitely until STOP set to 1 or SEQ7LOOP ≠0xF	0
3:0	SEQ8LOOP	RW	Control the loop number of the eighth sequence b0000~b1110: play (code+1) time b1111: playback infinitely until STOP set to 1 or SEQ8LOOP ≠0xF	0

WAVCFG13: (Address 16h)				
Bit	Symbol	R/W	Description	Default
7:6	Reserved	RW	Not used	0
5:4	WAITSLOT	RW	Unit of wait time b00: (1/WAVDAT_MODE) s b01: (8/WAVDAT_MODE) s b10: (64/WAVDAT_MODE) s b11: (512/WAVDAT_MODE) s	0
3:0	MAINLOOP	RW	Control the main loop number b0000~b1110: play (code+1) time b1111: playback infinitely until STOP set to 1 or MAINLOOP ≠0xF	0

CONTCFG1: (Address 18h)				
Bit	Symbol	R/W	Description	Default
7	Reserved	RW	Not used	0
6	BRK_BST_MD	RW	When set 1, bst_mode in brake is the same with current palyback mode, otherwise the bst_mode in brake is 0	0
5	EN_F0_DET	RW	F0 detection mode enable 1: enable 0: disable	0
4	SIN_MODE	RW	Edge mode for filtered square wave of CONT mode: 1: cos 0: sine	1

3:0	EDGE_FRE	RW	Define the edge frequency b1000 : 200Hz b1001 : 210Hz b1010 : 260Hz b1011 : 280Hz b1100 : 300Hz b1101 : 600Hz b1110 : 700Hz b1111 : 800Hz b0000-b0111: play non-filtered square wave in CONT mode	14

CONTCFG2: (Address 19h)

Bit	Symbol	R/W	Description	Default
7:0	F_PRE	RW	Set the value of F0, F0=(24K/code)Hz	0x8D

CONTCFG3: (Address 1Ah)

Bit	Symbol	R/W	Description	Default
7:0	DRV_WIDTH	RW	Half cycle drive time of brake and it is also the half cycle drive time of drive when TRACK_EN=0, this value must be smaller than half cycle time of F0. Time = code/48000 (s)	0x6A

CONTCFG5: (Address 1Ch)

Bit	Symbol	R/W	Description	Default
7:4	BST_BRK_GAIN	RW	Gain factor of brake when BST_MODE is 1	5
3:0	BRK_GAIN	RW	Gain factor of brake when BST_MODE is 0	8

CONTCFG6: (Address 1Dh)

Bit	Symbol	R/W	Description	Default
7	TRACK_EN	RW	Track switch 1: enable 0: disable	1
6:0	DRV1_LVL	RW	Level for the first cont drive. When VBAT_MODE=1: no load output voltage=VBAT_REF*DRV1_LVL/128; if (VBAT_REF*DRV1_LVL)/VBAT > 128, no load output voltage=PVDD; When VBAT_MODE=0/BST_MODE=1: no load output voltage=PVDD*DRV1_LVL/128	0x7F

CONTCFG7: (Address 1Eh)

Bit	Symbol	R/W	Description	Default
7	Reserved	RW	Not used	0
6:0	DRV2_LVL	RW	Level for the second cont drive When VBAT_MODE=1: no load output voltage=VBAT_REF*DRV2_LVL/128; if (VBAT_REF*DRV2_LVL)/VBAT > 128, no load output voltage=PVDD; When VBAT_MODE=0/BST_MODE=1: no load output voltage=PVDD*DRV2_LVL/128	0x50

CONTCFG8: (Address 1Fh)

Bit	Symbol	R/W	Description	Default
7:0	DRV1_TIME	RW	Number of half cycle for the first cont drive	4

CONTCFG9: (Address 20h)

Bit	Symbol	R/W	Description	Default
7:0	DRV2_TIME	RW	Number of half cycle for the second cont drive	6

CONTCFG10: (Address 21h)				
Bit	Symbol	R/W	Description	Default
7:0	BRK_TIME	RW	The num of half cycle of brake mode	8

CONTCFG11: (Address 22h)				
Bit	Symbol	R/W	Description	Default
7:0	TRACK_MARGIN	RW	Margin value of tracking, the smaller margin, the higher tracking accuracy and the lower loop stability. Time = code/480000 (s)	12

CONTRD14: (Address 25h)				
Bit	Symbol	R/W	Description	Default
7:0	F_LRA_F0_H	RO	High 8 bit of the measure value for the f0 of LRA in the f0 detection mode F0=(384000/(F_LRA_F0_H*256+F_LRA_F0_L))Hz	0

CONTRD15: (Address 26h)				
Bit	Symbol	R/W	Description	Default
7:0	F_LRA_F0_L	RO	Low 8 bit of the measure value for the f0 of LRA in the f0 detection mode F0=(384000/(F_LRA_F0_H*256+F_LRA_F0_L))Hz	0

CONTRD16: (Address 27h)				
Bit	Symbol	R/W	Description	Default
7:0	CONT_F0_H	RO	The measure value for the f0 of LRA in the continuous detection mode (high eight bits) F0=(384000/(CONT_F0_H*256+CONT_F0_L))Hz	0

CONTRD17: (Address 28h)				
Bit	Symbol	R/W	Description	Default
7:0	CONT_F0_L	RO	The measure value for the f0 of LRA in the continuous detection mode (low eight bits) F0=(384000/(CONT_F0_H*256+CONT_F0_L))Hz	0

RTPCFG1: (Address 2Dh)				
Bit	Symbol	R/W	Description	Default
7:5	Reserved	RW	Not used	0
4:0	BASE_ADDR_H	RW	High five bits of start address of wave SRAM BASE_ADDR = BASE_ADDR_H * 256 + BASE_ADDR_L	0x08

RTPCFG2: (Address 2Eh)				
Bit	Symbol	R/W	Description	Default
7:0	BASE_ADDR_L	RW	Low eight bits of start address of wave SRAM BASE_ADDR = BASE_ADDR_H * 256 + BASE_ADDR_L	0

RTPCFG3: (Address 2Fh)				
Bit	Symbol	R/W	Description	Default
7:4	FIFO_AEH	RW	High four bits of RTP FIFO almost empty threshold FIFO_AE = FIFO_AEH * 256 + FIFO_AEL	0x02
3:0	FIFO_AFH	RW	High four bits of RTP FIFO almost full threshold FIFO_AF = FIFO_AFH * 256 + FIFO_AFL	0x06

RTPCFG4: (Address 30h)				
Bit	Symbol	R/W	Description	Default
7:0	FIFO_AEL	RW	Low eight bits of RTP FIFO almost empty threshold FIFO_AE = FIFO_AEH * 256 + FIFO_AEL	0x00

RTPCFG5: (Address 31h)				
Bit	Symbol	R/W	Description	Default
7:0	FIFO_AFL	RW	Low eight bits of RTP FIFO almost full threshold FIFO_AF = FIFO_AFH * 256 + FIFO_AFL	0x00

RTPDATA: (Address 32h)				
Bit	Symbol	R/W	Description	Default
7:0	RTP_DATA	RW	RTP mode , data write entry, when data written into this register, the data will be written into RTP FIFO	0

TRGCFG1: (Address 33h)				
Bit	Symbol	R/W	Description	Default
7	TRG1_POS	RW	TRG1 rising edge enable/disable control 1: enable 0: disable	0
6:0	TRG1SEQ_P	RW	TRG1 posedge trigged wave sequence number	1

TRGCFG2: (Address 34h)				
Bit	Symbol	R/W	Description	Default
7	TRG2_POS	RW	TRG2 rising edge enable/disable control 1: enable 0: disable	0
6:0	TRG2SEQ_P	RW	TRG2 posedge trigged wave sequence number	1

TRGCFG3: (Address 35h)				
Bit	Symbol	R/W	Description	Default
7	TRG3_POS	RW	TRG3 rising edge enable/disable control 1: enable 0: disable	0
6:0	TRG3SEQ_P	RW	TRG3 posedge trigged wave sequence number	1

TRGCFG4: (Address 36h)				
Bit	Symbol	R/W	Description	Default
7	TRG1_NEG	RW	TRG1 falling edge enable/disable control 1: enable 0: disable	0
6:0	TRG1SEQ_N	RW	TRG1 negedge trigged wave sequence number	1

TRGCFG5: (Address 37h)				
Bit	Symbol	R/W	Description	Default
7	TRG2_NEG	RW	TRG2 falling edge enable/disable control 1: enable 0: disable	0
6:0	TRG2SEQ_N	RW	TRG2 negedge trigged wave sequence number	1

TRGCFG6: (Address 38h)				
Bit	Symbol	R/W	Description	Default
7	TRG3_NEG	RW	TRG3 falling edge enable/disable control 1: enable 0: disable	0
6:0	TRG3SEQ_N	RW	TRG3 negedge trigged wave sequence number	1

TRGCFG7: (Address 39h)				
Bit	Symbol	R/W	Description	Default
7	TRG1_POLAR	RW	TRIG1 pin active polarity, when host supply positive level, this bit set to 0, else set to 1	0
6	TRG1_LEV	RW	TRG1 mode control 1: level 0: edge	0
5	TRG1_BRK	RW	When set 1, enable auto brake after TRG1 playback mode is stopped	1
4	TRG1_BST	RW	When set 1, enable boost in TRG1 playback mode.	1
3	TRG2_POLAR	RW	TRIG2 pin active polarity, when host supply positive level, this bit set to 0, else set to 1.	0
2	TRG2_LEV	RW	TRG2 mode control 1: level 0: edge	0
1	TRG2_BRK	RW	When set 1, enable auto brake after TRG2 playback mode is stopped	1
0	TRG2_BST	RW	When set 1, enable boost in TRG2 playback mode.	1

TRGCFG8: (Address 3Ah)				
Bit	Symbol	R/W	Description	Default
7	TRG3_POLAR	RW	TRIG3 pin active polarity, when host supply positive level, this bit set to 0, else set to 1	0
6	TRG3_LEV	RW	TRG3 mode control 1: level 0: edge	0
5	TRG3_BRK	RW	When set 1, enable auto brake after TRG3 playback mode is stopped	1
4	TRG3_BST	RW	When set 1, enable boost in TRG3 playback mode.	1
3	TRG_ONEWIRE	RW	When set 1,enable one wire mode	0
2	TRG1_STOP	RW	When set 1, TRG1 playback mode can be stopped immediately	0
1	TRG2_STOP	RW	When set 1, TRG2 playback mode can be stopped immediately	0
0	TRG3_STOP	RW	When set 1, TRG3 playback mode can be stopped immediately	0

GLBCFG2: (Address 3Ch)				
Bit	Symbol	R/W	Description	Default
7:0	START_DLY	RW	Startup delay time, unit time is (1/48k)s	0x08

GLBCFG4: (Address 3Eh)				
Bit	Symbol	R/W	Description	Default
7:6	GO_PRIO	RW	Priority value of GO TRIG High priority can interrupt the playback of low priority, and low priority cannot interrupt the playback of high priority. When the priority settings are consistent, the default priority will be implemented	0
5:4	TRG3_PRIO	RW	Priority value of TRIG3 pin High priority can interrupt the playback of low priority, and low priority cannot interrupt the playback of high priority. When the priority settings are consistent, the default priority will be implemented	1
3:2	TRG2_PRIO	RW	Priority value of TRIG2 pin High priority can interrupt the playback of low priority, and low priority cannot interrupt the playback of high priority. When the priority settings are consistent, the default priority will be implemented	2
1:0	TRG1_PRIO	RW	Priority value of TRIG1 pin High priority can interrupt the playback of low priority, and low priority cannot interrupt the playback of high priority. When the priority settings are consistent, the default priority will be implemented	3

GLBRD5: (Address 3Fh)				
Bit	Symbol	R/W	Description	Default
7:4	Reserved	RO	Not used	0
3:0	GLB_STATE	RO	The state of glb state b0000: STANDBY b0110: CONT b0111: RAM b1000: RTP b1001: TRIG b1011: BRAKE	0

RAMADDRH: (Address 40h)				
Bit	Symbol	R/W	Description	Default
7:5	Reserved	RW	Not used	0
4:0	RAMADDRH	RW	SRAM address high five bits	0

RAMADDRL: (Address 41h)				
Bit	Symbol	R/W	Description	Default
7:0	RAMADDRL	RW	SRAM address low eight bits	0

RAMDATA: (Address 42h)				
Bit	Symbol	R/W	Description	Default
7:0	RAMDATA	RW	SRAM data entry	0

SYSCTRL3: (Address 45h)				
Bit	Symbol	R/W	Description	Default
7	Reserved	RW	Not used	0
6	WAKE	RW	Chip enable control 0: chip at normal mode 1: set chip into active mode	0
5	STANDBY	RW	Chip disable control 0: chip at normal mode 1: set chip into standby mode	0
4:3	Reserved		Not used	2
2	EN_RAMINIT	RW	Enable clock: 1: open the digital module clock 0: close the digital module clock	0
1	EN_FIR	RW	Set enable of FIR filter	1
0	Reserved	RW	Not used	0

SYSCTRL4: (Address 46h)				
Bit	Symbol	R/W	Description	Default
7	Reserved	RW	Not used	0
6:5	WAVDAT_MODE	RW	Waveform data upsample rate selection: b00: 24kHz b01: 48kHz others: 12kHz rate	0
4:0	Reserved	RW	Not used	8

SYSCTRL5: (Address 47h)				
Bit	Symbol	R/W	Description	Default
7	EN_BRO_ADR	RW	Enable broadcast address control 0: I2C communication through hardware device address 1: I2C communication through hardware device address or BROADCAST_ADDR	0
6:0	BROADCAST_ADDR	RW	Software device address configuration	0

PWMCFG1: (Address 48h)				
Bit	Symbol	R/W	Description	Default
7	PRC_EN	RW	Set enable of output signal protection mode of pwm: 0: disable 1: When HDP/HDN output voltage ≥ 124/128*PVDD maintains (PRCTIME/3k)s, HDP/HDN is pulled down protectively	0
6:0	PRCTIME	RW	Set protection time of output signal protection mode of pwm, unit time is (1/3k) s	0x00

PWMCFG2: (Address 49h)				
Bit	Symbol	R/W	Description	Default
7:5	reserved	RW	Not used	1
4	PD_HWM	RW	shutdown half wave modulate 0: half wave mode 1: full wave mode	0
3:0	reserved	RW	Not used	8

WMCFG3: (Address 4Ah)				
Bit	Symbol	R/W	Description	Default
7	PR_EN	RW	Set enable of input signal protection mode of pwm: 0: disable 1: When output voltage >= PRLVL/128*PVDD maintains (PRTIME/3k)s, HDP/HDN is pulled down protectively	1
6:0	PRLVL	RW	Set protection voltage of input signal protection mode of pwm	0x3F

PWMCFG4: (Address 4Bh)				
Bit	Symbol	R/W	Description	Default
7:0	PRTIME	RW	Set protection time of input signal protection mode of pwm, unit time is (1/3k) s	0x32

VBATCTRL: (Address 4Ch)				
Bit	Symbol	R/W	Description	Default
7	reserved	RW	Not used	0
6	VBAT_MODE	RW	VBAT adjust mode: 0: software adjust mode 1: hardware adjust mode	0
5:0	reserved	RW	Not used	0

DETCFG1: (Address 4Dh)				
Bit	Symbol	R/W	Description	Default
7	Reserved	RW	Not used	0
6:4	VBAT_REF	RW	Reference voltage for VBAT hardware adjust mode: b000: 3.3V b001: 3.6V b010: 4.0V b011: 4.2V b100: 4.5V b101: 4.8V b110: 5.0V b111: 5.5V When VBAT_MODE=1: no load output voltage=VBAT_REF*WAVE_DATA/128; if (VBAT_REF* WAVE_DATA)/VBAT > 128, no load output voltage=PVDD; When VBAT_MODE=0/BST_MODE=1: no load output voltage=PVDD*WAVE_DATA /128.	2
3:2	ADC_FS	RW	ADC clock sampling rate: b00: 192kHz(ADC_CLK=6.144MHz) b01: 96kHz(ADC_CLK=3.072MHz) b10: 48kHz(ADC_CLK=1.536MHz) b11: 24kHz(ADC_CLK=768kHz)	1

1:0	DET_GO	RW	ADC sampling mode control: b01: det others: not det	0

DETCFG2: (Address 4Eh)

Bit	Symbol	R/W	Description	Default
7	Reserved	RW	Not used	0
6:3	DET_SEQ0	RW	Sequence0 detect type control: b0000: VBAT b0001: PVDD b0011: RL b0100: OS Others: for test	0
2:0	D2S_GAIN	RW	Set D2S gain: b000: 1 b001: 2 b010: 4 b011: 8 b100: 10 b101: 16 b110: 20 b111: 40	4

DET_RD1: (Address 4Fh)

Bit	Symbol	R/W	Description	Default
7:4	Reserved	RO	Not used	0
3:2	ADC_DATA_H	RO	The measured value of one time adc data(high two bits)	0
1:0	AVG_DATA_H	RO	The measured value of 16 times adc average data(high two bits)	0

DET_RD2: (Address 50h)

Bit	Symbol	R/W	Description	Default
7:0	AVG_DATA_L	RO	The measured value of 16 times adc average data(low eight bits)	0

DET_RD3: (Address 51h)

Bit	Symbol	R/W	Description	Default
7:0	ADC_DATA_L	RO	The measured value of one times adc data(low eight bits)	0

IDH: (Address 57h)

Bit	Symbol	R/W	Description	Default
7:0	CHIPID_H	RO	High 8 bit of CHIP_ID	0x92

IDT_RD3: (Address 58h)

Bit	Symbol	R/W	Description	Default
7:0	CHIPID_L	RO	Low 8 bit of CHIP_ID	0x70

Application Information

Inductor Selection Guideline

Selecting inductor needs to consider Inductance, size, magnetic shielding, saturation current and temperature current.

a) Inductance

Inductance value is limited by the boost converter's internal loop compensation. In order to ensure phase margin sufficient under all operating conditions, recommended 1μH inductor.

b) Size

For a certain value of inductor, the smaller the size, the greater the parasitic series resistance of the inductor DCR, the higher the loss, corresponds to the lower efficiency.

c) Magnetic shielding

Magnetic shielding can effectively prevent the inductance of the electromagnetic radiation interference. It is much better to choose inductance with magnetic shielding in the application of EMI sensitive environment.

d) Saturation current and temperature rise of current

Inductor saturation current and temperature rise current value are important basis for selecting the inductor. As the inductor current increases, on the one hand, since the magnetic core begins to saturate, inductance value will decline; on the other hand, the inductor's parasitic resistance inductance and magnetic core loss can lead to temperature rise. In general, the current value is defined as the saturation current I_{SAT} when the inductance value drops to 70%; the current value is defined as temperature rise current I_{RMS} when inductance temperature rise 40°C.

For particular applications, need to calculate the maximum I_{L_PEAK} and I_{L_RMS}, which is a basis of selecting the inductor. When VBAT=3.8V, PVDD=8.5V, R_L = 8Ω，Output drive R_{DSON} =300mΩ, when the maximum power without distortion, the output power is calculated as follows:

$$P_{OUT} = \frac{(V_{OUT}\times\frac{R_L}{R_L+R_{DSON}})^2}{2\times R_L\times(1-2.3\%)} = \frac{(8.5\times\frac{8}{8+0.3})^2}{2\times8\times0.977}w = 4.294w$$

Where the coefficients in the denominator of (0.977) is the power ratio of no truncation maximum output. In such a large output power, the overall efficiency of the output drive is typically 75%, in order to calculate the maximum average current $I_{MAX\_AVG\_VBAT}$ and maximum peak current $I_{MAX\_PEAK\_VBAT}$ drawn from VBAT:

$$I_{MAX\_AVG\_VBAT} = \frac{P_{OUT}}{VBAT\times\eta} = \frac{4.294}{3.8\times0.75}A = 1.507A$$

$$I_{MAX\_PEAK\_VBAT} = 2\times I_{MAX\_AVG\_VBAT} = 2\times1.507\text{A} = 3.014\text{A}$$

If inductor DCR is 50mΩ, then when the output power of 4.294W, the inductor power loss is:

$$P_{DCR.LOSS} = 1.5\times I^2_{MAX\_AVG\_VBAT}\times DCR = 1.5\times1.507^2\times0.05\,W = 170.3\,mW$$

Wherein the coefficient 1.5 is the square of the ratio of the sine wave current RMS value and average value (there is no consideration of the impact of the inductor ripple, the actual DCR loss will be even greater). If the loss which is resulting from DCR is less than 1% at efficiency (POUT = 4.294W, η = 75%), then:

$$DCR = \frac{P_{DCR.LOSS}}{1.5\times I^2_{MAX\_AVG\_VBAT}} \le 0.01\times\frac{P_{OUT}}{1.5\times I^2_{MAX\_AVG\_VBAT}\times\eta} = \frac{0.01\times4.294}{1.5\times1.507^2\times0.75}\Omega = 16.8\,m\Omega$$

According to the working principle of the Boost, we can calculate the size of the inductor current ripple ΔI_L:

$$\triangle I_L = \frac{VBAT\times(PVDD-VBAT)}{PVDD\times f\times L} = \frac{3.8\times(8.5-3.8)}{8.5\times2\times1}A = 1.050A$$

Thus, the maximum peak inductor current I_{L_PEAK} and maximum effective inductor current I_{L_RMS} is:

$$I_{L\_PEAK} = I_{MAX\_PEAK\_VBAT} + \frac{\triangle I_L}{2} = 3.014 + \frac{1.050}{2}A = 3.539A$$

$$I_{L\_RMS} = \sqrt{I_{MAX\_PEAK\_VBAT}^2 + \frac{\triangle I_L^2}{12}} = \sqrt{3.014^2 + \frac{1.050^2}{12}} A = 3.029A$$

From the above calculation results:

1) For typical DCR about 50mΩ inductance, the efficiency loss caused by around 3%;
2) Need to choose AW86927N inductance input current limit value I_{LIMIT} is greater than I_{L_PEAK} = 3.6A (< I_{LIMIT} = 4A), to guarantee the output drive power can be achieved when THD = 1% (= 4.1W) but not limited by value I_{LIMIT}; If you choose I_{SAT} or I_{RMS} of the inductance is too small, it is possible to cause the chip don't work properly, or the temperature of the inductance is too high.
3) In practice, the maximum output power of the drive is likely to reach 4.3W in an instant, so the selected inductor saturation current I_{SAT} requires more than the maximum inductor peak current I_{L_PEAK}, and cannot be less than 3.6A;
4) In some cases, if the I_{L_PEAK} calculated according to the above method is greater than the set of input inductor current limit value I_{LIMIT}, shows the output drive is restricted by inductance input current limit, the actual maximum output power is less than the calculated value, the measured value shall prevail, and I_{SAT} need greater than the set current limiting value I_{LIMIT}, and cannot be less than 3.6A;
5) Take PVDD = 8.5V for example, under different conditions, the typical method of selecting I_{SAT} in the following table:

VBAT (V)	PVDD (V)	R_L (Ω)	I_{L_PEAK} (A)	Inductor saturation current I_{SAT} minimum value (A)
3.4	8.5	8	3.9	4.5
3.4	8.5	16	2.3	2.5

Capacitors Selection

Boost Capacitor Selection

Boost output capacitor is usually within the range 0.1μF~47μF. It needs to use Class II type (EIA) multilayer ceramic capacitors (MLCC). Its internal dielectric is ferroelectric material (typically $BaTiO_3$), a high the dielectric constant in order to achieve smaller size, but at the same Class II type (EIA) multilayer ceramic capacitors has poor temperature stability and voltage stability as compared to the Class I type (EIA) capacitance. Capacitor is selected based on the requirements of temperature stability and voltage stability, considering the capacitance material, capacitor voltage, and capacitor size and capacitance values.

A) temperature stability

Class II capacitance have different temperature stability in different materials, usually choose X5R type in order to ensure enough temperature stability, and X7R type capacitance has better properties, the price is relatively more expensive; X5R capacitance change within ± 15% in temperature range of -55°C to 85°C, X7R capacitance change within ±15% in temperature range of -55°C~125°C. The Boost output capacitance of AW86927N recommends X5R ceramic capacitors.

B) Voltage Stability

Class II type capacitor has poor voltage stability Capacitance values falling fast along with the DC bias voltage applied across the capacitor increasing. The rate of decline is related to capacitance material, capacitors rated voltage, capacitance volume. Take for TDK C series X5R for example, its pressure voltage value is 16V or 25V; the package size is 0805, 1206 or 0603, the capacitance value is 10μF. The capacitor's voltage stability of different types of capacitor is as shown below:

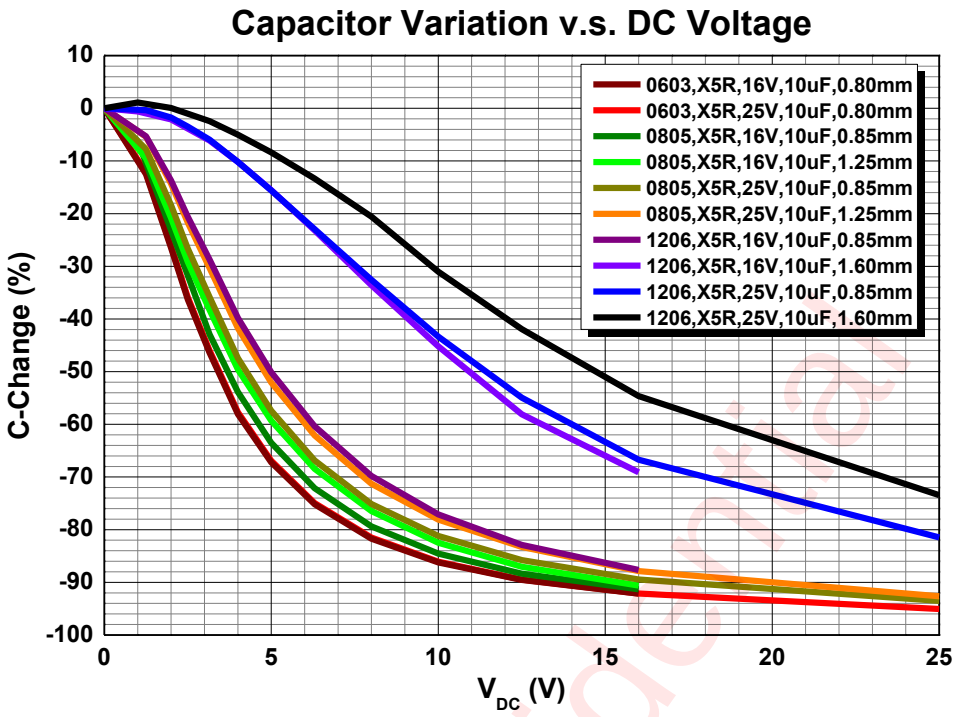


Figure 28 Different types of capacitive voltage stability

Among them, the space remaining value of different types of capacitors at V_{DC} = 8.5 V as shown in the Figure 29:

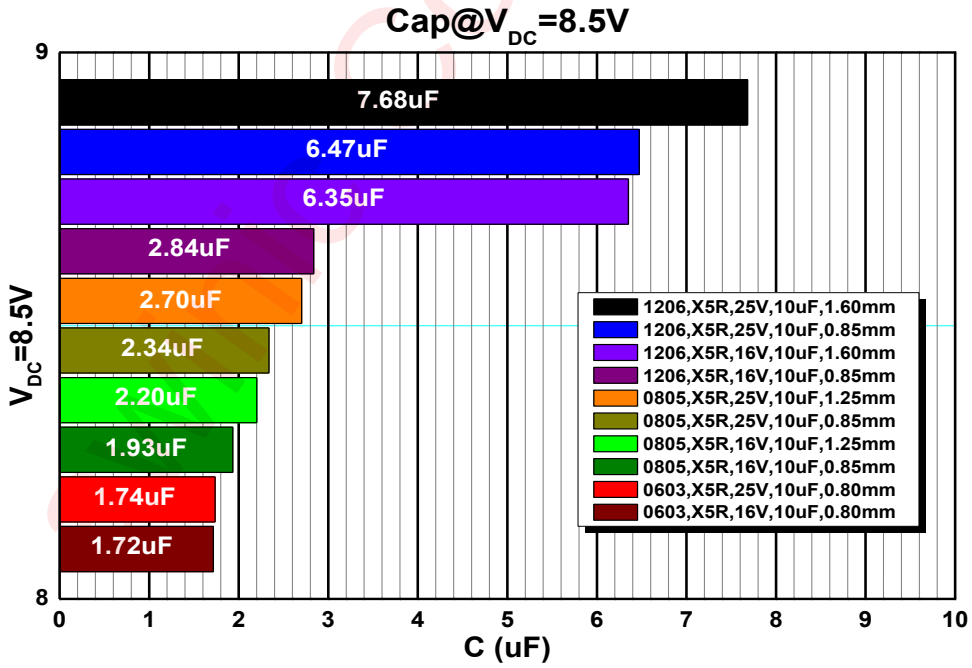


Figure 29 The space remaining value of different types of capacitors at VDC = 8.5 V

It can be found that the rate of capacitance capacity value descent becomes slow along with "large capacitor size, capacitance pressure voltage rise". The larger the package size, the better voltage stability. The higher the height, the better voltage stability with the same length and width of the capacitance. Voltage stability of smaller package size (0603) capacitor change affected by the pressure value is very small.

In AW86927N typical applications, it is necessary to ensure the output value of the Boost capacitor ≥ 5μF when PVDD=8.5V.

Supply Decoupling Capacitor（C_S）

The device is a high voltage driver that requires adequate power supply decoupling. Place a low equivalent-series-resistance (ESR) ceramic capacitor, typically 0.1μF. This choice of capacitor and placement helps with higher frequency transients, spikes, or digital hash on the line. Additionally, placing this decoupling capacitor close to the device is important, as any parasitic resistance or inductance between the device and the capacitor causes efficiency loss. In addition to the 0.1μF ceramic capacitor, place a 10μF capacitor on the VBAT supply trace. This larger capacitor acts as a charge reservoir, providing energy faster than the board supply, thus helping to prevent any droop in the supply voltage.

Output beads, capacitors

The device output is a square wave signal, which causing switch current at the output capacitor, increasing static power consumption, and therefore output capacitor should not be too large, 0.1nF ceramic capacitors is recommended.

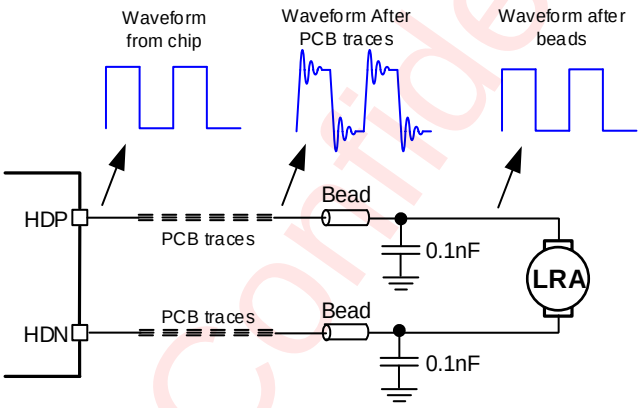


Figure 30 Ferrite Chip Bead and capacitor

The device output is a square wave signal. The voltage across the capacitor will be much larger than the PVDD voltage after increasing the bead capacitor. It suggested the use of rated voltage above 16V capacitor. At the same time a square wave signal at the output capacitor switching current form, the static power consumption increases, so the output capacitance should not be too much which is recommended 0.1nF ceramic capacitor rated voltage of 16V.

PCB Layout Consideration

Layout Considerations

This device is a high voltage driver chip. To obtain the optimal performance, PCB layout should be considered carefully. The suggested Layout is illustrated in the following diagram:

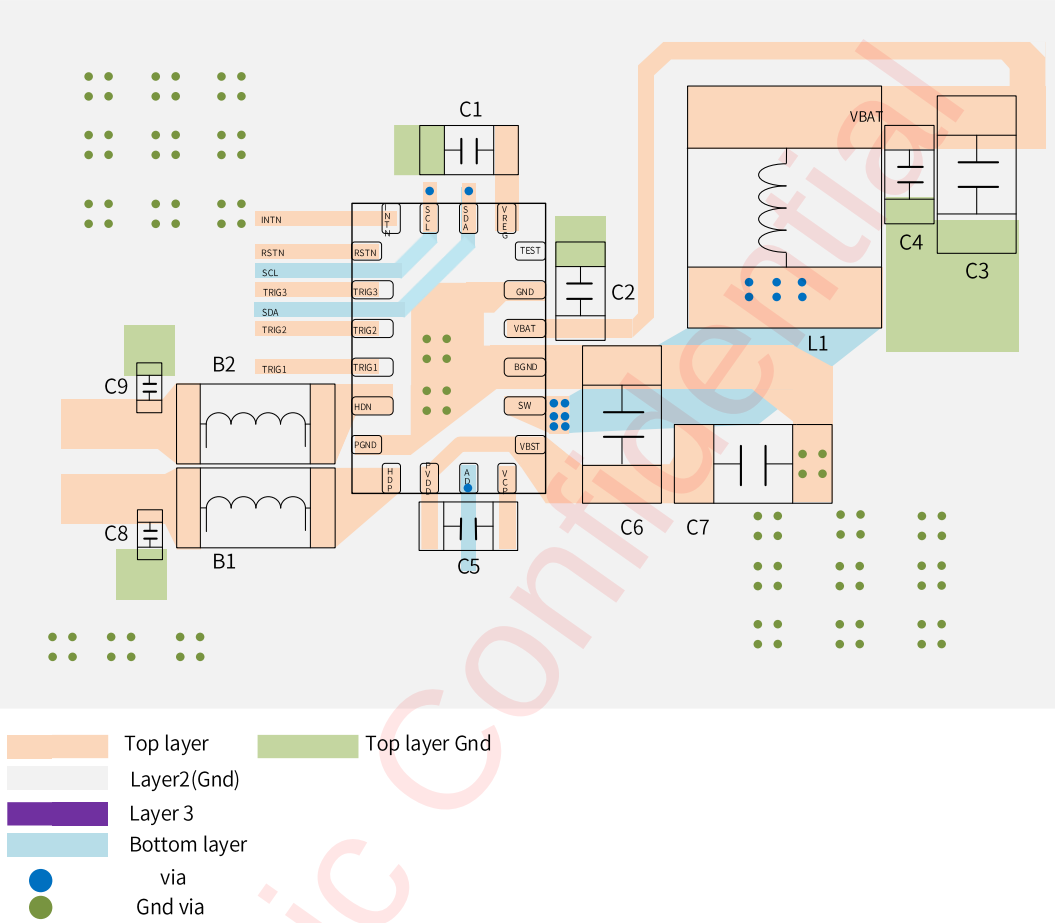


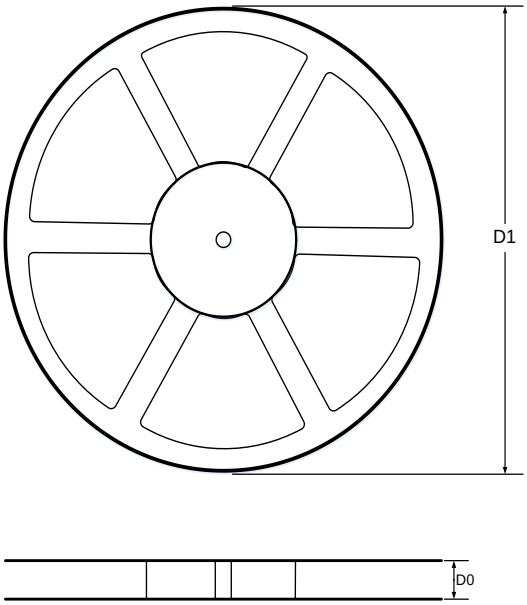
Figure 31 AW86927N Board Layout

Here are some guidelines:

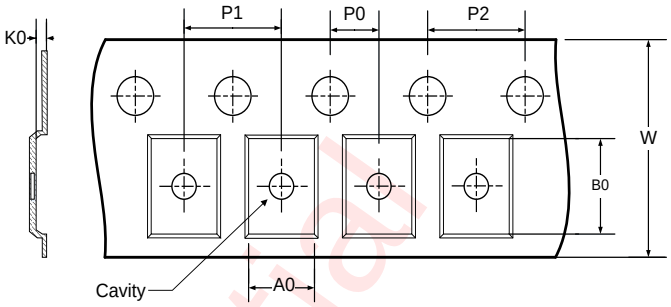
1. All of the external components should be placed as close as possible to IC in top layer PCB.
2. SCL and SDA should be shield by ground.
3. The overcurrent capability of the VBAT to SW should meet $I_{MAX\_PEAK\_VBAT}$, and C2, C3, C4 should be placed close to IC and L1.
4. C6 and C7 are within 1.5mm to pin PVDD or pin VBST, and the overcurrent capability of the VBST and PVDD traces must be meet $\frac{PVDD}{R_L+R_{DSON}}$, and the GND side of the PVDD capacitor should be directly connected to surface layer ground or punched to the main ground of the PCB. In addition, create solid GND plane near and around the IC, connect BGND, PGND and GND together, and the overcurrent capability of the vias should be designed according to the PVDD overcurrent capability.
5. Routing overcurrent capability of HDP/HDN output to the load should meet $\frac{PVDD}{R_L+R_{DSON}}$. HDP and HDN should be shield by ground and far away from the interference source especially the FLY capacitor of the high-power charging IC, otherwise it will cause the abnormal F0 detection.

Tape And Reel Information

REEL DIMENSIONS

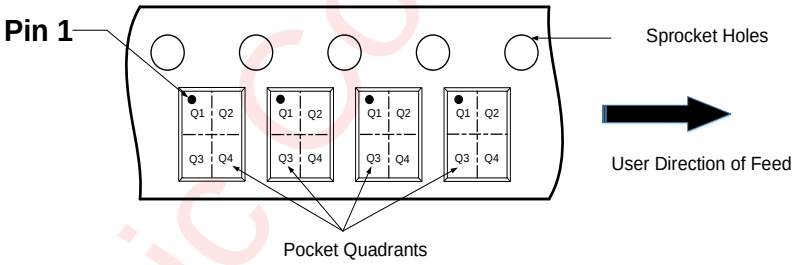


TAPE DIMENSIONS



A0：Dimension designed to accommodate the component width
B0：Dimension designed to accommodate the component length
K0：Dimension designed to accommodate the component thickness
W：Overall width of the carrier tape
P0：Pitch between successive cavity centers and sprocket hole
P1：Pitch between successive cavity centers
P2：Pitch between sprocket hole
D1：Reel Diameter
D0：Reel Width

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

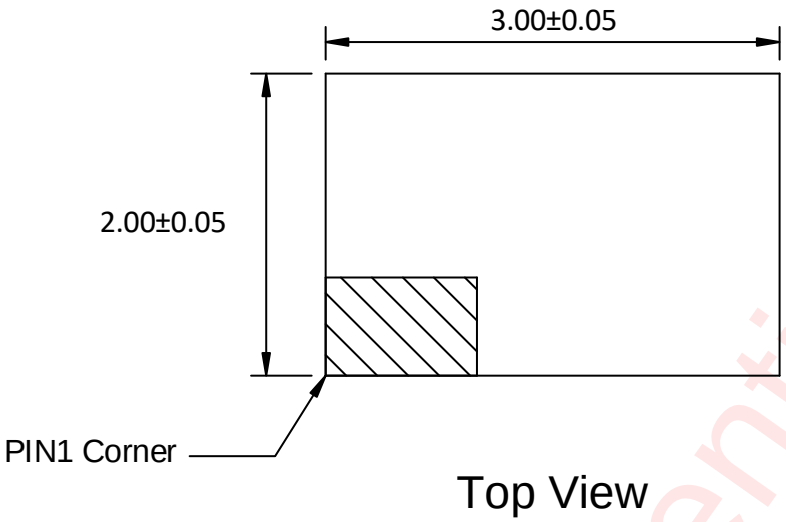


DIMENSIONS AND PIN1 ORIENTATION

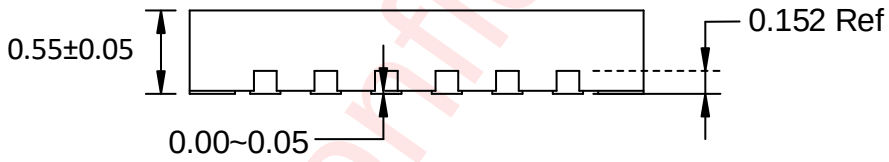
D1 (mm)	D0 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
330	12.4	2.3	3.3	0.75	2	4	4	12	Q1

All dimensions are nominal

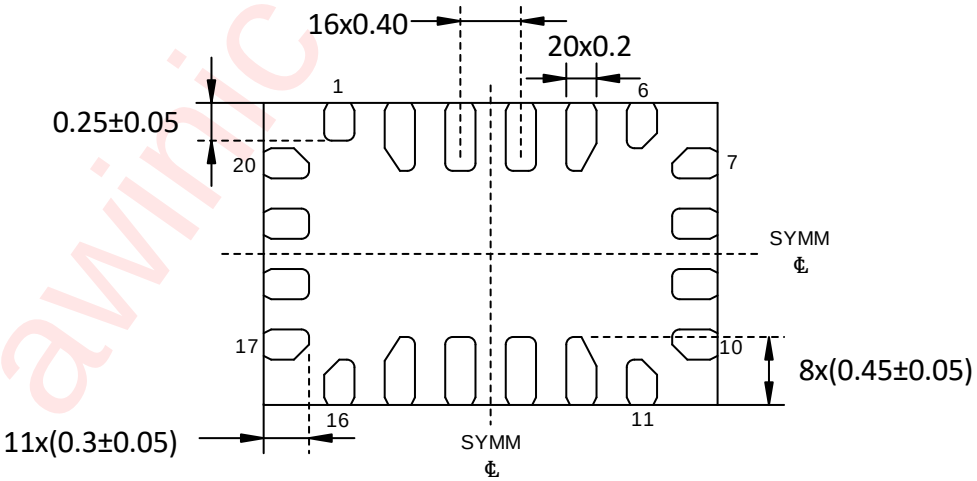
Package Description



Top View



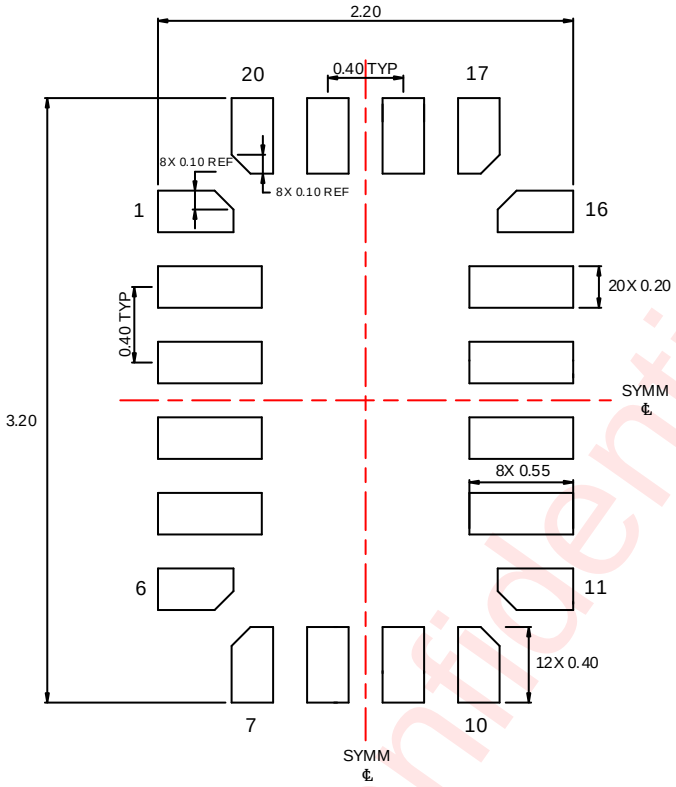
Side View

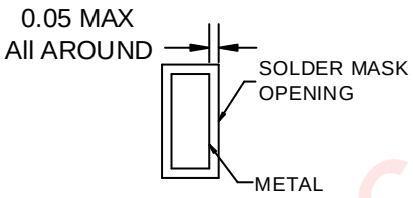


Bottom View

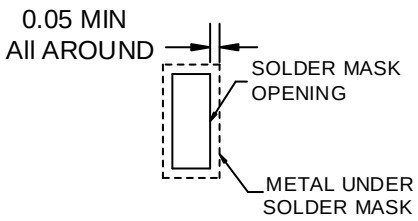
Unit:mm

Land Pattern Data





NON-SOLDER MASK DEFINED



SOLDER MASK DEFINED

Unit：mm

Revision History

Version	Date	Change Record
V1.0	April 2022	Official Version
V1.1	April 2023	Revise Application introduction and waveform library initialization steps

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